

# ACT8930

Rev 5, 17-Sep-13

## **Advanced PMU for Portable Handheld Equipment**

#### **FEATURES**

- Three Step-Down DC/DC Converters
- Four Low-Dropout Linear Regulators
- Dedicated enable pins for the voltage regulators for flexible power sequencing.
- Integrated *ActivePath*<sup>TM</sup> Charger
- I<sup>2</sup>C<sup>™</sup> Serial Interface
- Minimal External Components
- Tiny 5×5mm TQFN55-40 Package
  - 0.75mm Package Height
  - Pb-Free and RoHS Compliant

#### GENERAL DESCRIPTION

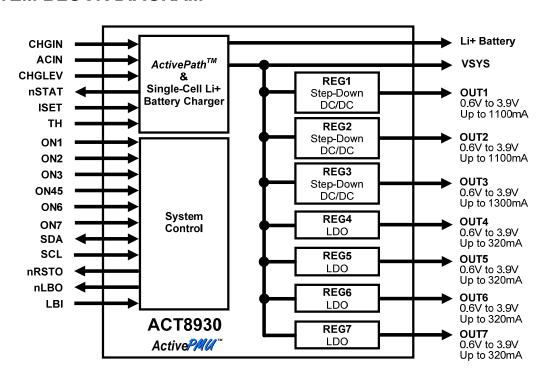
The ACT8930 is a complete, cost effective, highly-efficient  $ActivePMU^{TM}$  power management solution, for portable handheld equipment such as Smartphones, Mobile Internet Devices (MID), eBooks and etc.

This device features three step-down DC/DC converters and four low-noise, low-dropout linear regulators, along with a complete battery charging solution featuring the advanced *ActivePath*<sup>TM</sup> system-power selection function.

The three DC/DC converters utilize a high-efficiency, fixed-frequency (2MHz), current-mode PWM control architecture that requires a minimum number of external components. Two DC/DCs are capable of supplying up to 1100mA of output current, while the third supports up to 1300mA. All four low-dropout linear regulators are high-performance, low-noise regulators that supply up to 320mA each.

The ACT8930 is available in a compact, Pb-Free and RoHS-compliant TQFN55-40 package.

#### SYSTEM BLOCK DIAGRAM



- 1 -

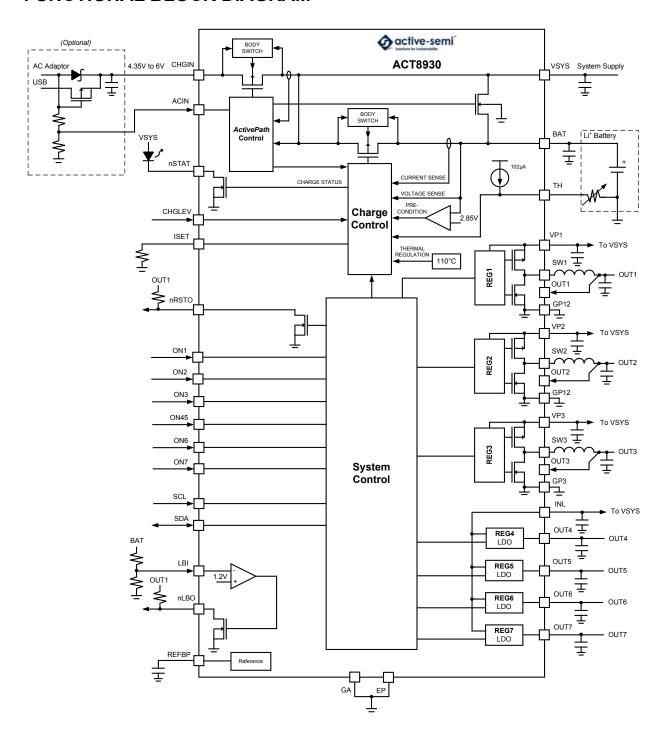


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#### **FUNCTIONAL BLOCK DIAGRAM**

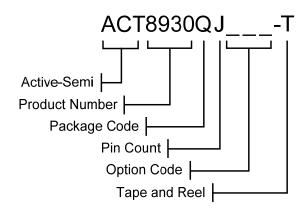




## ORDERING INFORMATION®®

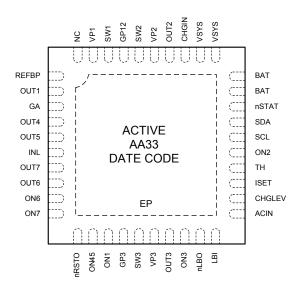
PART NUMBER	V <sub>OUT1</sub>	V <sub>OUT2</sub>	V <sub>OUT3</sub>	V <sub>OUT4</sub>	V <sub>OUT5</sub>	V <sub>OUT6</sub>	V <sub>OUT7</sub>	PACKAGE	PINS	TEMPERATURE RANGE
ACT8930QJ133-T	3.3V	1.3V	1.3V	1.2V	1.2V	1.2V	3.3V	TQFN55-40	40	-40°C to +85°C
ACT8930QJ134-T	1.35V	3.3V	1.8V	3.3V	1.8V	3.3V	3.3V	TQFN55-40	40	-40°C to +85°C
ACT8930QJ135-T	1.8V	1.2	1.2V	1.2V	3.3V	3.3V	1.8V	TQFN55-40	40	-40°C to +85°C

- ①: All Active-Semi components are RoHS Compliant and with Pb-free plating unless otherwise specified.
- ②: Standard product options are listed in this table. Contact factory for custom options. Minimum order quantity is 12,000 units.



#### PIN CONFIGURATION

#### **TOP VIEW**



Thin - QFN (TQFN55-40)



## **PIN DESCRIPTIONS**

PIN	NAME	DESCRIPTION
1	REFBP	Reference Bypass. Connect a 0.047μF ceramic capacitor from REFBP to GA. This pin is discharged to GA in shutdown.
2	OUT1	Output Feedback Sense for REG1.
3	GA	Analog Ground. Connect GA directly to a quiet ground node. Connect GA, GP12 and GP3 together at a single point as close to the IC as possible.
4	OUT4	REG4 output. Capable of delivering up to 320mA of output current. Connect a 3.3μF ceramic capacitor from OUT4 to GA. The output is discharged to GA with 1.5kΩ resistor when disabled.
5	OUT5	REG5 output. Capable of delivering up to 320mA of output current. Connect a 3.3μF ceramic capacitor from OUT5 to GA. The output is discharged to GA with 1.5kΩ resistor when disabled.
6	INL	Power Input for REG4, REG5, REG6, and REG7. Bypass to GA with a high quality ceramic capacitor placed as close to the IC as possible.
7	OUT7	REG7 output. Capable of delivering up to 320mA of output current. Connect a 3.3μF ceramic capacitor from OUT7 to GA. The output is discharged to GA with 1.5kΩ resistor when disabled.
8	OUT6	REG6 output. Capable of delivering up to 320mA of output current. Connect a 3.3μF ceramic capacitor from OUT6 to GA. The output is discharged to GA with 1.5kΩ resistor when disabled.
9	ON6	Enable Input for REG6. Drive to VP1 or a logic high to enable REG6. Drive to GA to disable.
10	ON7	Enable Input for REG7. Drive to VP1 or a logic high to enable REG7. Drive to GA to disable.
11	nRSTO	Active Low Reset Output. See the nRSTO Output section for more information.
12	ON45	Enable Input for REG4 and REG5. Drive to VP1 or a logic high to enable REG4 and REG5. Drive to GA to disable.
13	ON1	Enable Input for REG1. Drive to VP1 or a logic high to enable REG1. Drive to GA to disable.
14	GP3	Power Ground for REG3. Connect GA, GP12, and GP3 together at a single point as close to the IC as possible.
15	SW3	Switching Node Output for REG3.
16	VP3	Power Input for REG3. Bypass to GP3 with a high quality ceramic capacitor placed as close to the IC as possible.
17	OUT3	Output Feedback Sense for REG3.
18	ON3	Enable Input for REG3. Drive to VP1 or a logic high to enable REG3. Drive to GA to disable.
19	nLBO	Low Battery Indicator Output. nLBO is asserted low whenever the voltage at LBI is lower than 1.2V, and is high-Z otherwise. See the <i>Precision Voltage Detector</i> section for more information.
20	LBI	Low Battery Input. The input voltage is compared to 1.2V and the output of this comparison drives nLBO. See the <i>Precision Voltage Detector</i> section for more information.
21	ACIN	AC Input Supply Detection. See the Charge Current Programming section for more information.
22	CHGLEV	Charge Current Selection Input. See the Charge Current Programming section for more information.



## PIN DESCRIPTIONS CONT'D

PIN	NAME	DESCRIPTION
23	ISET	Charge Current Set. Program the charge current by connecting a resistor (R <sub>ISET</sub> ) between ISET and GA. See the <i>Charge Current Programming</i> section for more information.
24	TH	Temperature Sensing Input. Connect to battery thermistor. TH is pulled up with a 102µA (typ) current internally. See the <i>Battery Temperature Monitoring</i> section for more information.
25	ON2	Enable Input for REG2. Drive to VP1 or a logic high to enable REG2. Drive to GA to disable.
26	SCL	Clock Input for I <sup>2</sup> C Serial Interface.
27	SDA	Data Input for I <sup>2</sup> C Serial Interface. Data is read on the rising edge of SCL.
28	nSTAT	Active-Low Open-Drain Charger Status Output. nSTAT has a 8mA (typ) current limit, allowing it to directly drive an indicator LED without additional external components. See the <i>Charge Status Indicator</i> section for more information.
29, 30	BAT	Battery Charger Output. Connect this pin directly to the battery anode (+ terminal)
31, 32	VSYS	System Output Pin. Bypass to GA with a 10µF or larger ceramic capacitor.
33	CHGIN	Power Input for the Battery Charger. Bypass CHGIN to GA with a capacitor placed as close to the IC as possible. The battery charger is automatically enabled when a valid voltage is present on CHGIN .
34	OUT2	Output Feedback Sense for REG2.
35	VP2	Power Input for REG2. Bypass to GP12 with a high quality ceramic capacitor placed as close to the IC as possible.
36	SW2	Switching Node Output for REG2.
37	GP12	Power Ground for REG1 and REG2. Connect GA, GP12 and GP3 together at a single point as close to the IC as possible.
38	SW1	Switching Node Output for REG1.
39	VP1	Power Input for REG1. Bypass to GP12 with a high quality ceramic capacitor placed as close to the IC as possible.
40	NC	No Connect. Not internally connected.
EP	EP	Exposed Pad. Must be soldered to ground on PCB.



## **ABSOLUTE MAXIMUM RATINGS®**

PARAMETER	VALUE	UNIT
VP1, VP2 to GP12 VP3 to GP3	-0.3 to +6	V
BAT, VSYS, INL to GA	-0.3 to +6	V
CHGIN to GA	-0.3 to +14	V
SW1, OUT1 to GP12	-0.3 to (V <sub>VP1</sub> + 0.3)	V
SW2, OUT2 to GP12	-0.3 to (V <sub>VP2</sub> + 0.3)	V
SW3, OUT3 to GP3	-0.3 to (V <sub>VP3</sub> + 0.3)	V
nLBO, nRSTO, nSTAT to GA	-0.3 to +6	V
ON45, ON1, ON6, ACIN, CHGLEV, ISET, LBI, ON7, ON3, REFBP, SCL, SDA, TH, ON2 to GA	-0.3 to (VSYS+0.3)	V
OUT4, OUT5, OUT6, OUT7 to GA	-0.3 to (V <sub>INL</sub> + 0.3)	V
GP12, GP3 to GA	-0.3 to +0.3	V
Operating Ambient Temperature	-40 to 85	°C
Maximum Junction Temperature	125	°C
Maximum Power Dissipation TQFN55-40 (Thermal Resistance $\theta_{JA}$ = 30°C/W)	2.7	W
Storage Temperature	-65 to 150	°C
Lead Temperature (Soldering, 10 sec)	300	°C

①: Do not exceed these limits to prevent damage to the device. Exposure to absolute maximum rating conditions for long periods may affect device reliability.

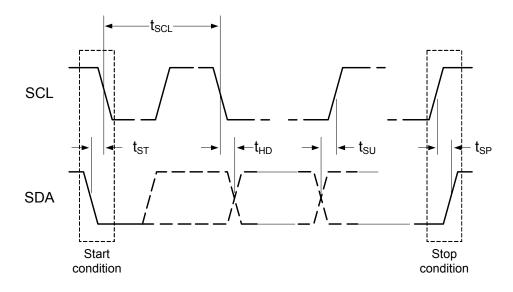


## I<sup>2</sup>C INTERFACE ELECTRICAL CHARACTERISTICS

( $V_{VSYS}$  = 3.6V,  $T_A$  = 25°C, unless otherwise specified.)

PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
SCL, SDA Input Low	$V_{VSYS}$ = 3.1V to 5.5V, $T_A$ = -40°C to 85°C			0.35	V
SCL, SDA Input High	$V_{VSYS}$ = 3.1V to 5.5V, $T_A$ = -40°C to 85°C	1.55			V
SDA Leakage Current				1	μA
SCL Leakage Current			8	18	μΑ
SDA Output Low	I <sub>OL</sub> = 5mA			0.35	V
SCL Clock Period, t <sub>SCL</sub>		1.5			μs
SDA Data Setup Time, t <sub>SU</sub>		100			ns
SDA Data Hold Time, t <sub>HD</sub>		300			ns
Start Setup Time, t <sub>ST</sub>	For Start Condition	100			ns
Stop Setup Time, t <sub>SP</sub>	For Stop Condition	100			ns

Figure 1: I<sup>2</sup>C Compatible Serial Bus Timing





## **GLOBAL REGISTER MAP**

						В	BITS			
OUTPUT	ADDRESS		D7	D6	D5	D4	D3	D2	D1	D0
0)/0	000	NAME	TRST	nSYSMODE	Reserved	nSYSSTAT	SYSLEV[3]	SYSLEV[2]	SYSLEV[1]	SYSLEV[0]
SYS	0x00	DEFAULT <sup>®</sup>	0	1	0	R	0	1	1	1
CVC	0,01	NAME	Reserved	Reserved	Reserved	Reserved	SCRATCH	SCRATCH	SCRATCH	SCRATCH
SYS	0x01	DEFAULT <sup>®</sup>	0	0	0	0	0	0	0	0
DEO4	2504 0.00	NAME	Reserved	Reserved	VSET[5]	VSET[4]	VSET[3]	VSET[2]	VSET[1]	VSET[0]
REG1	0x20	DEFAULT <sup>®</sup>	0	0	1	1	1	0	0	1
DE04	000	NAME	ON	PHASE	MODE	Reserved	Reserved	Reserved	Reserved	OK
REG1	UXZZ	DEFAULT <sup>®</sup>	0	0	0	0	1	1	0	R
DE 00	0.00	NAME	Reserved	Reserved	VSET[5]	VSET[4]	VSET[3]	VSET[2]	VSET[1]	VSET[0]
REG2	0x30	DEFAULT <sup>®</sup>	0	0	0	1	1	0	1	0
DEGG	0.00	NAME	ON	PHASE	MODE	Reserved	Reserved	Reserved	Reserved	OK
REG2	0x32	DEFAULT <sup>®</sup>	0	0	0	0	1	1	0	R
DEGG	040	NAME	Reserved	Reserved	VSET[5]	VSET[4]	VSET[3]	VSET[2]	VSET[1]	VSET[0]
REG3	0X40	DEFAULT <sup>®</sup>	0	0	0	1	1	0	1	0
DECO	0.40	NAME	ON	Reserved	MODE	Reserved	Reserved	Reserved	Reserved	OK
REG3	UX42	DEFAULT <sup>®</sup>	0	0	0	0	0	0	0	R
DEC4	0,450	NAME	Reserved	Reserved	VSET[5]	VSET[4]	VSET[3]	VSET[2]	VSET[1]	VSET[0]
REG4	UXSU	DEFAULT <sup>®</sup>	0	0	0	1	1	0	0	0
REG4	0v51	NAME	ON	DIS	LOWIQ	Reserved	Reserved	Reserved	Reserved	OK
INLU4	0.01	DEFAULT <sup>®</sup>	0	1	0	0	0	0	0	R
DEC5	0×54	NAME	Reserved	Reserved	VSET[5]	VSET[4]	VSET[3]	VSET[2]	VSET[1]	VSET[0]
INLUG	REG5 0x54	DEFAULT <sup>®</sup>	0	0	0	1	1	0	0	0
REG5	0×55	NAME	ON	DIS	LOWIQ	Reserved	Reserved	Reserved	Reserved	OK
INLOS	G1 0x22 N/OEF/ G2 0x30 DEF/ G2 0x32 DEF/ G3 0x40 DEF/ G3 0x42 DEF/ G4 0x50 DEF/ G5 0x54 DEF/ G5 0x55 DEF/ G6 0x60 DEF/ G7 0x64 DEF/ G7 0x65 DEF/ CH 0x70 DEF/ CH 0x71 N/OEF/ CH 0x71 N/OEF	DEFAULT <sup>®</sup>	0	1	0	0	0	0	0	R
REG6	0x60	NAME	Reserved	Reserved	VSET[5]	VSET[4]	VSET[3]	VSET[2]	VSET[1]	VSET[0]
INLOG	0,000	DEFAULT <sup>®</sup>	0	0	0	1	1	0	SYSLEV[1]   1	0
REG6	0x61	NAME	ON	DIS	LOWIQ	Reserved	Reserved	Reserved	Reserved	OK
-11200	0x30 DE 0x32 DE 0x40 DE 0x40 DE 0x42 DE 0x50 DE 0x51 DE 0x54 DE 0x55 DE 0x60 DE 0x61 DE 0x64 DE 0x70 DE	DEFAULT <sup>®</sup>	0	1	0	0	0	0	-	R
REG7	0x64	NAME	Reserved	Reserved	VSET[5]	VSET[4]	VSET[3]	VSET[2]		VSET[0]
- 11201	ONO I	DEFAULT <sup>®</sup>	0	0	1	1	1	0		1
REG7	0x65	NAME	ON	DIS	LOWIQ	Reserved	Reserved	Reserved		OK
	onoo	DEFAULT <sup>®</sup>	0	1	0	0	0	0	_	R
APCH	0x70	NAME	Reserved	Reserved	Reserved	Reserved	Reserved	Reserved		
		DEFAULT <sup>®</sup>	0	1	0	1	0	0	0	0
APCH	0v71	NAME	SUSCHG	Reserved	TOTTIMO[1]	TOTTIMO[0]	PRETIMO[1]	PRETIMO[0]	OVPSET[1]	OVPSET[0]
AI OII	0.771	DEFAULT <sup>®</sup>	0	0	1	0	1	0	0	0
ADOLI	0,70	NAME	Reserved	Reserved	Reserved	Reserved	TIMRDAT	TEMPDAT	INDAT	CHGDAT
APCH	0x78	DEFAULT <sup>®</sup>	0	0	0	0	R	R	R	R
ADOLI	0.74	NAME	Reserved	Reserved	CSTATE[0]	CSTATE[1]	Reserved	Reserved	ACINSTAT	Reserved
APCH	0x7A	DEFAULT <sup>®</sup>	0	0	R	R	R	R	R	R

①: Default values of ACT8930QJ133-T.

②: All bits are automatically cleared to default values when the input power is removed or falls below the system UVLO.



## **REGISTER AND BIT DESCRIPTIONS**

Table 1: **Global Register Map** 

OUTPUT	ADDRESS	BIT	NAME	ACCESS	DESCRIPTION
SYS	0x00	[7]	TRST	R/W	Reset Timer Setting. Defines the reset time-out threshold. Reset time-out is 65ms when value is 1, reset time-out is 260ms when value is 0. See <i>nRSTO Output</i> section for more information.
SYS	0x00	[6]	nSYSMODE	R/W	SYSLEV Mode Select. Defines the response to the SYSLEV voltage detector, 1: Do nothing, 0: automatic shutdown when $V_{\text{VSYS}}$ falls below the programmed SYSLEV threshold.
SYS	0x00	[5]	-	R	Reserved.
SYS	0x00	[4]	nSYSSTAT	R	System Voltage Status. Value is 1 when $V_{VSYS}$ is lower than the SYSLEV voltage threshold, value is 0 when $V_{VSYS}$ is higher than the system voltage detection threshold.
SYS	0x00	[3:0]	SYSLEV	R/W	System Voltage Detect Threshold. Defines the SYSLEV voltage threshold. See the <i>Programmable System Voltage Monitor</i> section for more information.
SYS	0x01	[7:4]	-	R/W	Reserved.
SYS	0x01	[3:0]	SCRATCH	R/W	Scratchpad Bits. Non-functional bits, maybe be used by user to store system status information. Volatile bits, which are cleared when system voltage falls below UVLO threshold.
REG1	0x20	[7:6]	-	R	Reserved.
REG1	0x20	[5:0]	VSET	R/W	Output Voltage Selection. See the <i>Output Voltage Programming</i> section for more information.
REG1	0x22	[7]	ON	R/W	Regulator Enable Bit. Set bit to 1 to enable the regulator, clear bit to 0 to disable the regulator.
REG1	0x22	[6]	PHASE	R/W	Regulator Phase Control. Set bit to 1 for the regulator to operate 180° out of phase with the oscillator, clear bit to 0 for the regulator to operate in phase with the oscillator.
REG1	0x22	[5]	MODE	R/W	Regulator Mode Select. Set bit to 1 for fixed-frequency PWM under all load conditions, clear bit to 0 to transit to power-savings mode under light-load conditions.
REG1	0x22	[4:1]	-	R	Reserved.
REG1	0x22	[0]	ОК	R	Regulator Power-OK Status. Value is 1 when output voltage exceeds the power-OK threshold, value is 0 otherwise.
REG2	0x30	[7:6]	-	R	Reserved.
REG2	0x30	[5:0]	VSET	R/W	Output Voltage Selection. See the <i>Output Voltage Programming</i> section for more information.
REG2	0x32	[7]	ON	R/W	Regulator Enable Bit. Set bit to 1 to enable the regulator, clear bit to 0 to disable the regulator.
REG2	0x32	[6]	PHASE	R/W	Regulator Phase Control. Set bit to 1 for the regulator to operate 180° out of phase with the oscillator, clear bit to 0 for the regulator to operate in phase with the oscillator.



## **REGISTER AND BIT DESCRIPTIONS CONT'D**

OUTPUT	ADDRESS	BIT	NAME	ACCESS	DESCRIPTION
REG2	0x32	[5]	MODE	R/W	Regulator Mode Select. Set bit to 1 for fixed-frequency PWM under all load conditions, clear bit to 0 to transit to power-savings mode under light-load conditions.
REG2	0x32	[4:1]	1	R	Reserved.
REG2	0x32	[0]	OK	R	Regulator Power-OK Status. Value is 1 when output voltage exceeds the power-OK threshold, value is 0 otherwise.
REG3	0x40	[7:6]	-	R	Reserved.
REG3	0x40	[5:0]	VSET	R/W	Output Voltage Selection. See the <i>Output Voltage Programming</i> section for more information.
REG3	0x42	[7]	ON	R/W	Regulator Enable Bit. Set bit to 1 to enable the regulator, clear bit to 0 to disable the regulator.
REG3	0x42	[6]	-	R	Reserved.
REG3	0x42	[5]	MODE	R/W	Regulator Mode Select. Set bit to 1 for fixed-frequency PWM under all load conditions, clear bit to 0 to transit to power-savings mode under light-load conditions.
REG3	0x42	[4:1]	-	R	Reserved.
REG3	0x42	[0]	OK	R	Regulator Power-OK Status. Value is 1 when output voltage exceeds the power-OK threshold, value is 0 otherwise.
REG4	0x50	[7:6]	-	R	Reserved.
REG4	0x50	[5:0]	VSET	R/W	Output Voltage Selection. See the <i>Output Voltage Programming</i> section for more information.
REG4	0x51	[7]	ON	R/W	Regulator Enable Bit. Set bit to 1 to enable the regulator, clear bit to 0 to disable the regulator.
REG4	0x51	[6]	DIS	R/W	Output Discharge Control. When activated, LDO output is discharged to GA through $1.5k\Omega$ resistor when in shutdown. Set bit to 1 to enable output voltage discharge in shutdown, clear bit to 0 to disable this function.
REG4	0x51	[5]	LOWIQ	R/W	LDO Low-IQ Mode Control. Set bit to 1 for low-power operating mode, clear bit to 0 for normal mode.
REG4	0x51	[4:1]	-	R	Reserved.
REG4	0x51	[0]	OK	R	Regulator Power-OK Status. Value is 1 when output voltage exceeds the power-OK threshold, value is 0 otherwise.
REG5	0x54	[7:6]	-	R	Reserved.
REG5	0x54	[5:0]	VSET	R/W	Output Voltage Selection. See the <i>Output Voltage Programming</i> section for more information.
REG5	0x55	[7]	ON	R/W	Regulator Enable Bit. Set bit to 1 to enable the regulator, clear bit to 0 to disable the regulator.
REG5	0x55	[6]	DIS	R/W	Output Discharge Control. When activated, LDO output is discharged to GA through 1.5k $\Omega$ resistor when in shutdown. Set bit to 1 to enable output voltage discharge in shutdown, clear bit to 0 to disable this function.
REG5	0x55	[5]	LOWIQ	R/W	LDO Low-IQ Mode Control. Set bit to 1 for low-power operating mode, clear bit to 0 for normal mode.
REG5	0x55	[4:1]	-	R	Reserved.
REG5	0x55	[0]	ОК	R	Regulator Power-OK Status. Value is 1 when output voltage exceeds the power-OK threshold, value is 0 otherwise.



## **REGISTER AND BIT DESCRIPTIONS CONT'D**

OUTPUT	ADDRESS	ВІТ	NAME	ACCESS	DESCRIPTION
REG6	0x60	[7:6]	-	R	Reserved.
REG6	0x60	[5:0]	VSET	R/W	Output Voltage Selection. See the Output Voltage Programming section for more information.
REG6	0x61	[7]	ON	R/W	Regulator Enable Bit. Set bit to 1 to enable the regulator, clear bit to 0 to disable the regulator.
REG6	0x61	[6]	DIS	R/W	Output Discharge Control. When activated, LDO output is discharged to GA through $1.5 \mathrm{k}\Omega$ resistor when in shutdown. Set bit to 1 to enable output voltage discharge in shutdown, clear bit to 0 to disable this function.
REG6	0x61	[5]	LOWIQ	R/W	LDO Low-IQ Mode Control. Set bit to 1 for low-power operating mode, clear bit to 0 for normal mode.
REG6	0x61	[4:1]	-	R	Reserved.
REG6	0x61	[0]	ОК	R	Regulator Power-OK Status. Value is 1 when output voltage exceeds the power-OK threshold, value is 0 otherwise.
REG7	0x64	[7:6]	-	R	Reserved.
REG7	0x64	[5:0]	VSET	R/W	Output Voltage Selection. See the <i>Output Voltage Programming</i> section for more information.
REG7	0x65	[7]	ON	R/W	Regulator Enable Bit. Set bit to 1 to enable the regulator, clear bit to 0 to disable the regulator.
REG7	0x65	[6]	DIS	R/W	Output Discharge Control. When activated, LDO output is discharged to GA through 1.5k $\Omega$ resistor when in shutdown. Set bit to 1 to enable output voltage discharge in shutdown, clear bit to 0 to disable this function.
REG7	0x65	[5]	LOWIQ	R/W	LDO Low-IQ Mode Control. Set bit to 1 for low-power operating mode, clear bit to 0 for normal mode.
REG7	0x65	[4:1]	-	R	Reserved.
REG7	0x65	[0]	ОК	R	Regulator Power-OK Status. Value is 1 when output voltage exceeds the power-OK threshold, value is 0 otherwise.
APCH	0x70	[7:0]	-	R/W	Reserved.
APCH	0x71	[7]	SUSCHG	R/W	Charge Suspend Control Input. Set bit to 1 to suspend charging, clear bit to 0 to allow charging to resume.
APCH	0x71	[6]	-	R/W	Reserved.
APCH	0x71	[5:4]	TOTTIMO	R/W	Total Charge Time-out Selection. See the <i>Charge Safety Timers</i> section for more information.
APCH	0x71	[3:2]	PRETIMO	R/W	Precondition Charge Time-out Selection. See the <i>Charge Safety Timers</i> section for more information.
APCH	0x71	[1:0]	OVPSET	R/W	Input Over-Voltage Protection Threshold Selection. See the Input Over-Voltage Protection section for more information.
APCH	0x78	[7:4]	-	R	Reserved.
APCH	0x78	[3]	TIMRDAT®	R	Charge Timer Status. Value is 1 when precondition time-out or total charge time-out occurs. Value is 0 in other case.
APCH	0x78	[2]	TEMPDAT <sup>®</sup>	R	Temperature Status. Value is 0 when battery temperature is outside of valid range. Value is 1 when battery temperature is inside of valid range.

 $<sup>\</sup>odot$  : Valid only when CHGIN UVLO Threshold<br/>- $\mbox{V}_{\mbox{CHGIN}}\mbox{-CHGIN}$  OVP Threshold.



## **REGISTER AND BIT DESCRIPTIONS CONT'D**

OUTPUT	ADDRESS	BIT	NAME	ACCESS	DESCRIPTION
APCH	0x78	[1]	INDAT	R	Input Voltage Status. Value is 1 when a valid input at CHGIN is present. Value is 0 when a valid input at CHGIN is not present.
APCH	0x78	[0]	CHGDAT <sup>®</sup>	R	Charge State Machine Status. Value is 1 indicates the charger state machine is in EOC state, value is 0 indicates the charger state machine is in other states.
APCH	0x7A	[7:6]	-	R	Reserved.
APCH	0x7A	[5:4]	CSTATE	R	Charge State. Values indicate the current charging state. See the State Machine Status section for more information.
APCH	0x7A	[3:2]	-	R	Reserved.
APCH	0x7A	[1]	ACINSTAT	R	ACIN Status. Indicates the state of the ACIN input, typically in order to identify the type of input supply connected. Value is 1 when ACIN is above the 1.2V precision threshold, value is 0 when ACIN is below this threshold.
APCH	0x7A	[0]	-	R	Reserved.



## SYSTEM CONTROL ELECTRICAL CHARACTERISTICS

 $(V_{VSYS} = 3.6V, T_A = 25^{\circ}C, unless otherwise specified.)$ 

PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Input Voltage Range		2.7		5.5	V
UVLO Threshold Voltage	V <sub>VSYS</sub> Rising	2.2	2.45	2.65	V
UVLO Hysteresis	V <sub>VSYS</sub> Falling		200		mV
Supply Current	All Regulators Enabled		420		μA
Shutdown Supply Current	All Regulators Disabled		8	18	μA
Oscillator Frequency		1.8	2	2.2	MHz
Logic High Input Voltage <sup>®</sup>		1.4			V
Logic Low Input Voltage				0.4	V
Leakage Current	V <sub>nRSTO</sub> = 4.2V			1	μA
LBI Threshold Voltage	V <sub>BAT</sub> Falling	1.03	1.2	1.31	V
LBI Hysteresis Threshold	V <sub>BAT</sub> Rising		200		mV
Low Level Output Voltage®	I <sub>SINK</sub> = 5mA			0.35	V
nRSTO Delay			260 <sup>3</sup>		ms
Thermal Shutdown Temperature	Temperature rising		160		°C
Thermal Shutdown Hysteresis			20		°C

①: ON1, ON3, ON3, ON45, ON6, ON7 are logic inputs.

②: nLBO, nRSTO are open drain outputs.

 $<sup>\</sup>ensuremath{\mathfrak{I}}$  : Typical value shown. Actual value may vary from 227.9ms to 291.2ms.



## STEP-DOWN DC/DC ELECTRICAL CHARACTERISTICS

 $(V_{VP1} = V_{VP2} = V_{VP3} = 3.6V, T_A = 25^{\circ}C, unless otherwise specified.)$ 

Operating Voltage Range         2.7         5.5         V           UVLO Threshold         Input Voltage Rising         2.5         2.6         2.7         V           UVLO Hysteresis         Input Voltage Falling         100         mV           Standby Supply Current         Regulator Enabled         65         90         μA           Shutdown Current         V <sub>VP</sub> = 5.5V, Regulator Disabled         0         1         μA           Output Voltage Accuracy         Vour ≥ 1.2V, Iour = 10mA         -1%         V <sub>Now</sub> **         1%         V           Line Regulation         V <sub>VP</sub> = Max (Y <sub>Now</sub> ** -1, 3.2V) to 5.5V         0.15         %/V         %/V           Load Regulation         I <sub>OUT</sub> = 10mA to IMAX**         0.0017         %/V         %/V           Power Good Threshold         V <sub>OUT</sub> Rising         93         %/V         %/V           Power Good Hysteresis         V <sub>OUT</sub> Falling         2         %/V <sub>Now</sub> %/V <sub>Now</sub> Oscillator Frequency         V <sub>OUT</sub> Falling         1.8         2         2.2         MHz           Minimum On-Time         75         ns         ns         REG1           Maximum Output Current         1.1         1.5         A           Current Limit	PARAMETER	CONDITIONS	MIN	TYP	MAX	UNIT
UVLO Hysteresis         Input Voltage Falling         100         mV           Standby Supply Current         Regulator Enabled         65         90         μA           Shutdown Current         V <sub>VP</sub> = 5.5V, Regulator Disabled         0         1         μA           Output Voltage Accuracy         V <sub>VP</sub> = 5.5V, Regulator Disabled         0         1         μA           Output Voltage Accuracy         V <sub>VP</sub> = 5.5V, Regulator Disabled         -1%         V <sub>NcoM</sub> = 19%         V <sub>VP</sub> Line Regulation         V <sub>VP</sub> = Max (V <sub>NooM</sub> * 1, 3.2V) to 5.5V         0.15         %/V         W/V           Load Regulation         I <sub>OuT</sub> = 10mA to IMAX*         0.0017         %/mA         %/mA           Power Good Threshold         V <sub>OuT</sub> Rising         93         %/V <sub>NoM</sub> %/mA           Power Good Hysteresis         V <sub>OuT</sub> Ealling         2         %/V <sub>NoM</sub> %/v <sub>NoM</sub> 1.8         2         2.2         MHz         M/v <sub>NoM</sub> Mount 2         %/v <sub>NoM</sub> %/v <sub>NoM</sub> Mount 2         %/v <sub>NoM</sub> Mount 2         %/v <sub>NoM</sub> %/v <sub>NoM</sub> 0.01         %/v <sub>NoM</sub> Mount 2         %/v <sub>NoM</sub> 0.01         %/v <sub>NoM</sub> %/v <sub>NoM</sub> 0.01         %/v <sub>NoM</sub> Mount 2         %/v <sub>NoM</sub> 0.01<	Operating Voltage Range		2.7		5.5	V
$ \begin{array}{c} \text{Standby Supply Current} & \text{Regulator Enabled} & 65 & 90 & \mu A \\ \text{Shutdown Current} & V_{VP} = 5.5V, \text{Regulator Disabled} & 0 & 1 & \mu A \\ V_{OUT} \geq 1.2V, I_{OUT} = 10\text{mA} & -1\% & V_{NOM}^{\circ} & 1\% & V_{VU}^{\circ} \\ \hline V_{OUT} \leq 1.2V, I_{OUT} = 10\text{mA} & -2\% & V_{NOM}^{\circ} & 2\% & V_{VOM}^{\circ} & 2\% & V_{VOM}^{\circ}$	UVLO Threshold	Input Voltage Rising	2.5	2.6	2.7	V
	UVLO Hysteresis	Input Voltage Falling		100		mV
Output Voltage Accuracy         Vout ≥ 1.2V, Iout = 10mA         -1%         V <sub>NOM</sub> ®         1%         V           Line Regulation         V <sub>VP</sub> = Max (V <sub>NOM</sub> ® +1, 3.2V) to 5.5V         0.15         %/V           Load Regulation         I <sub>OUT</sub> = 10mA to IMAX®         0.0017         %/M           Power Good Threshold         Vour Rising         93         %V <sub>NOM</sub> Power Good Hysteresis         Vour Falling         2         %V <sub>NOM</sub> Oscillator Frequency         Vour ≥ 20% of V <sub>NOM</sub> 1.8         2         2.2         MHz           Vour ≥ 0V         500         kHz         500         kHz	Standby Supply Current	Regulator Enabled		65	90	μΑ
Output Voltage Accuracy         Vout < 1.2V, Iour = 10mA         -2% Vnow = 2%         Volum = 2%           Line Regulation         V <sub>VP</sub> = Max (V <sub>NOM</sub> = +1, 3.2V) to 5.5V         0.15         %/V           Load Regulation         I <sub>OUT</sub> = 10mA to IMAX = 0.0017         0.0017         %/mA           Power Good Threshold         Vour Rising         93         %V <sub>NOM</sub> Power Good Hysteresis         Vour Falling         2         %V <sub>NOM</sub> Oscillator Frequency         Vour ≥ 20% of V <sub>NOM</sub> 1.8         2         2.2         MHz           Ostillator Frequency         Vour ≥ 20% of V <sub>NOM</sub> 1.8         2         2.2         MHz           Soft-Start Period         400         µs         MMz         400         µs           Soft-Start Period         400         µs         ms	Shutdown Current	V <sub>VP</sub> = 5.5V, Regulator Disabled		0	1	μΑ
Line Regulation         V <sub>OUT</sub> < 1.2V, I <sub>OUT</sub> = 10mA         -2% V <sub>NOM</sub> **         2% V <sub>NOM</sub> **           Line Regulation         V <sub>VP</sub> = Max (V <sub>NOM</sub> ** +1, 3.2V) to 5.5V         0.15         %/V           Load Regulation         I <sub>OUT</sub> = 10mA to IMAX*         0.0017         %/mA           Power Good Threshold         V <sub>OUT</sub> Rising         93         %V <sub>NOM</sub> Power Good Hysteresis         V <sub>OUT</sub> Falling         2         %V <sub>NOM</sub> Oscillator Frequency         500         kHz           Soft-Start Period         1.8         2         2.2         MH-2           Soft-Start Period         400         µs           Minimum On-Time         75         ns         ns           REG1         Naximum Output Current         1.1         A           Current Limit         1.55         1.8         2.05         A           PMOS On-Resistance         I <sub>SW1</sub> = -100mA         0.16         Ω           SW1 Leakage Current         V <sub>VP1</sub> = 5.5V, V <sub>SW1</sub> = 0 or 5.5V         0         1         µA           REG2         NMaximum Output Current         1.55         1.8         2.05         A           PMOS On-Resistance         I <sub>SW2</sub> = -100mA         0.16         Ω         Ω           N	Output Valtage Assurage	V <sub>OUT</sub> ≥ 1.2V, I <sub>OUT</sub> = 10mA	-1%	$V_{NOM}{}^{\scriptscriptstyle{\textcircled{\tiny{1}}}}$	1%	\/
Load Regulation         I <sub>OUT</sub> = 10mA to IMAX°         0.0017         %/mA           Power Good Threshold         V <sub>OUT</sub> Rising         93         %V <sub>NOM</sub> Power Good Hysteresis         V <sub>OUT</sub> Falling         2         %V <sub>NOM</sub> Oscillator Frequency         V <sub>OUT</sub> ≥ 20% of V <sub>NOM</sub> 1.8         2         2.2         MHz           Soft-Start Period         400         µs           Minimum On-Time         75         ns           REG1         πs         πs           Maximum Output Current         1.1         A           Current Limit         1.55         1.8         2.05         A           PMOS On-Resistance         I <sub>SW1</sub> = -100mA         0.16         Ω           NMOS On-Resistance         I <sub>SW1</sub> = 100mA         0.16         Ω           SW1 Leakage Current         V <sub>VP1</sub> = 5.5V, V <sub>SW1</sub> = 0 or 5.5V         0         1         µA           REG2           Maximum Output Current         1.1         A         A           Current Limit         1.55         1.8         2.05         A           PMOS On-Resistance         I <sub>SW2</sub> = -100mA         0.16         Ω           NMOS On-Resistance         I <sub>SW2</sub> = 5.5V, V <sub>SW2</sub> = 0 or 5.5V         0 <td>Output voltage Accuracy</td> <td>V<sub>OUT</sub> &lt; 1.2V, I<sub>OUT</sub> = 10mA</td> <td>-2%</td> <td><math>V_{NOM}{}^{\scriptscriptstyle{\textcircled{\tiny{1}}}}</math></td> <td>2%</td> <td>]</td>	Output voltage Accuracy	V <sub>OUT</sub> < 1.2V, I <sub>OUT</sub> = 10mA	-2%	$V_{NOM}{}^{\scriptscriptstyle{\textcircled{\tiny{1}}}}$	2%	]
Power Good Threshold         V <sub>OUT</sub> Rising         93         %V <sub>NOM</sub> Power Good Hysteresis         V <sub>OUT</sub> Falling         2         %V <sub>NOM</sub> Oscillator Frequency $V_{OUT} ≥ 20\%$ of V <sub>NOM</sub> 1.8         2         2.2         MHz           Vout ≥ 20% of V <sub>NOM</sub> 1.8         2         2.2         MHz           Soft-Start Period         400         μs           Minimum On-Time         75         ns           REG1         1.1         A           Maximum Output Current         1.1         A           Current Limit         1.55         1.8         2.05         A           PMOS On-Resistance         I <sub>SW1</sub> = -100mA         0.16         Ω           SW1 Leakage Current         V <sub>VP1</sub> = 5.5V, V <sub>SW1</sub> = 0 or 5.5V         0         1         μA           REG2           Maximum Output Current         1.1         A         A           Current Limit         1.55         1.8         2.05         A           PMOS On-Resistance         I <sub>SW2</sub> = -100mA         0.16         Ω           NMOS On-Resistance         I <sub>SW2</sub> = 100mA         0.16         Ω           SW2 Leakage Current         V <sub>VP2</sub> = 5.5V, V <sub>SW2</sub> = 0 or 5.5V <td< td=""><td>Line Regulation</td><td><math>V_{VP} = Max (V_{NOM}^{\circ} + 1, 3.2V) \text{ to } 5.5V</math></td><td></td><td>0.15</td><td></td><td>%/V</td></td<>	Line Regulation	$V_{VP} = Max (V_{NOM}^{\circ} + 1, 3.2V) \text{ to } 5.5V$		0.15		%/V
Power Good Hysteresis         V <sub>OUT</sub> Falling         2         %V <sub>NOM</sub> Oscillator Frequency $V_{OUT} \ge 20\%$ of $V_{NOM}$ 1.8         2         2.2         MHz           Soft-Start Period         400         μs           Minimum On-Time         75         ns           REG1         1.1         A           Maximum Output Current         1.55         1.8         2.05         A           PMOS On-Resistance $I_{SW1} = -100mA$ 0.16         Ω           NMOS On-Resistance $I_{SW1} = 100mA$ 0.16         Ω           SW1 Leakage Current $V_{VP1} = 5.5V$ , $V_{SW1} = 0$ or $5.5V$ 0         1         μA           REG2         NMOS On-Resistance $I_{SW1} = 100mA$ 0.16         Ω           NAXimum Output Current         1.1         A         A           Current Limit         1.55         1.8         2.05         A           PMOS On-Resistance $I_{SW2} = -100mA$ 0.16         Ω           NMOS On-Resistance $I_{SW2} = 100mA$ 0.16         Ω           NMOS On-Resistance $I_{SW3} = -100mA$ 0.16         Ω           NMOS On-Resistance $I_{SW3} = -100mA$ <	Load Regulation	I <sub>OUT</sub> = 10mA to IMAX <sup>©</sup>		0.0017		%/mA
Vout ≥ 20% of V <sub>NOM</sub> 1.8         2         2.2         MHz           Soft-Start Period         400         µs           Minimum On-Time         75         ns           REG1           Maximum Output Current         1.1         A           Current Limit         1.55         1.8         2.05         A           PMOS On-Resistance $I_{SW1} = -100mA$ 0.16         Ω           NMOS On-Resistance $I_{SW1} = 100mA$ 0.16         Ω           SW1 Leakage Current $V_{VP1} = 5.5V, V_{SW1} = 0 \text{ or } 5.5V$ 0         1         µA           REG2           Maximum Output Current         1.1         A         A           Current Limit         1.55         1.8         2.05         A           PMOS On-Resistance $I_{SW2} = -100mA$ 0.16         Ω           NMOS On-Resistance $I_{SW2} = 100mA$ 0.16         Ω           SW2 Leakage Current $V_{VP2} = 5.5V, V_{SW2} = 0 \text{ or } 5.5V$ 0         1         µA           REG3           Maximum Output Current         1.3         A         A           Current Limit         1.3	Power Good Threshold	V <sub>OUT</sub> Rising		93		%V <sub>NOM</sub>
Oscillator Frequency         Vout = 0V         500         kHz           Soft-Start Period         400         μs           Minimum On-Time         75         ns           REG1           Maximum Output Current         1.1         A           Current Limit         1.55         1.8         2.05         A           PMOS On-Resistance         I <sub>SW1</sub> = -100mA         0.16         Ω           NMOS On-Resistance         I <sub>SW1</sub> = 100mA         0.16         Ω           SW1 Leakage Current         V <sub>VP1</sub> = 5.5V, V <sub>SW1</sub> = 0 or 5.5V         0         1         μA           REG2           Maximum Output Current         1.1         A         A           Current Limit         1.55         1.8         2.05         A           PMOS On-Resistance         I <sub>SW2</sub> = -100mA         0.16         Ω           NMOS On-Resistance         I <sub>SW2</sub> = 100mA         0.16         Ω           SW2 Leakage Current         V <sub>VP2</sub> = 5.5V, V <sub>SW2</sub> = 0 or 5.5V         0         1         μA           REG3           Maximum Output Current         1.3         A           Current Limit         1.8         2.1         2.5         A           PMOS On-Resist	Power Good Hysteresis	V <sub>OUT</sub> Falling		2		%V <sub>NOM</sub>
Vout = 0V   500   kHz	Ossillator Fraguency	V <sub>OUT</sub> ≥ 20% of V <sub>NOM</sub>	1.8	2	2.2	MHz
Minimum On-Time         75         ns           REG1         REG1         A         A           Maximum Output Current         1.1         A         A           Current Limit         1.55         1.8         2.05         A           PMOS On-Resistance         I <sub>SW1</sub> = -100mA         0.16         Ω           NMOS On-Resistance         I <sub>SW1</sub> = 100mA         0.16         Ω           SW1 Leakage Current         V <sub>VP1</sub> = 5.5V, V <sub>SW1</sub> = 0 or 5.5V         0         1         µA           REG2         Maximum Output Current         1.1         A         A           Current Limit         1.55         1.8         2.05         A           PMOS On-Resistance         I <sub>SW2</sub> = -100mA         0.16         Ω           NMOS On-Resistance         I <sub>SW2</sub> = 100mA         0.16         Ω           SW2 Leakage Current         V <sub>VP2</sub> = 5.5V, V <sub>SW2</sub> = 0 or 5.5V         0         1         µA           REG3           Maximum Output Current         1.3         A           Current Limit         1.8         2.1         2.5         A           PMOS On-Resistance         I <sub>SW3</sub> = -100mA         0.16         Ω           NMOS On-Resistance         I <sub>SW3</sub> = -100mA	Oscillator Frequency	V <sub>OUT</sub> = 0V		500		kHz
REG1         Maximum Output Current         1.1         A           Current Limit         1.55         1.8         2.05         A           PMOS On-Resistance $I_{SW1} = -100 \text{mA}$ 0.16         Ω           NMOS On-Resistance $I_{SW1} = 100 \text{mA}$ 0.16         Ω           SW1 Leakage Current $V_{VP1} = 5.5V$ , $V_{SW1} = 0$ or $5.5V$ 0         1         μA           REG2           Maximum Output Current         1.1         A         A           Current Limit         1.55         1.8         2.05         A           PMOS On-Resistance $I_{SW2} = -100 \text{mA}$ 0.16         Ω           NMOS On-Resistance $I_{SW2} = 100 \text{mA}$ 0.16         Ω           SW2 Leakage Current $V_{VP2} = 5.5V$ , $V_{SW2} = 0$ or $5.5V$ 0         1         μA           REG3           Maximum Output Current         1.3         A           Current Limit         1.8         2.1         2.5         A           PMOS On-Resistance $I_{SW3} = -100 \text{mA}$ 0.16         Ω           NMOS On-Resistance $I_{SW3} = 100 \text{mA}$ 0.16         Ω	Soft-Start Period			400		μs
Maximum Output Current         1.1         A           Current Limit         1.55         1.8         2.05         A           PMOS On-Resistance $I_{SW1} = -100 \text{mA}$ 0.16         Ω           NMOS On-Resistance $I_{SW1} = 100 \text{mA}$ 0.16         Ω           SW1 Leakage Current $V_{VP1} = 5.5 \text{V}$ , $V_{SW1} = 0 \text{ or } 5.5 \text{V}$ 0         1         μA           REG2           Maximum Output Current         1.1         A         A           Current Limit         1.55         1.8         2.05         A           PMOS On-Resistance $I_{SW2} = -100 \text{mA}$ 0.16         Ω           NMOS On-Resistance $I_{SW2} = 100 \text{mA}$ 0.16         Ω           REG3           Maximum Output Current         1.3         A           Current Limit         1.8         2.1         2.5         A           PMOS On-Resistance $I_{SW3} = -100 \text{mA}$ 0.16         Ω           NMOS On-Resistance $I_{SW3} = 100 \text{mA}$ 0.16         Ω	Minimum On-Time			75		ns
Current Limit         1.55         1.8         2.05         A           PMOS On-Resistance $I_{SW1} = -100 \text{mA}$ 0.16         Ω           NMOS On-Resistance $I_{SW1} = 100 \text{mA}$ 0.16         Ω           SW1 Leakage Current $V_{VP1} = 5.5 \text{V}$ , $V_{SW1} = 0 \text{ or } 5.5 \text{V}$ 0         1 $\mu A$ REG2           Maximum Output Current         1.1         A         A           Current Limit         1.55         1.8         2.05         A           PMOS On-Resistance $I_{SW2} = -100 \text{mA}$ 0.16         Ω           NMOS On-Resistance $I_{SW2} = 100 \text{mA}$ 0.16         Ω           SW2 Leakage Current $V_{VP2} = 5.5 \text{V}$ , $V_{SW2} = 0 \text{ or } 5.5 \text{V}$ 0         1 $\mu A$ REG3           Maximum Output Current         1.3         A           Current Limit         1.8         2.1         2.5         A           PMOS On-Resistance $I_{SW3} = -100 \text{mA}$ 0.16         Ω           NMOS On-Resistance $I_{SW3} = 100 \text{mA}$ 0.16         Ω	REG1	•				
PMOS On-Resistance $I_{SW1}$ = -100mA         0.16         Ω           NMOS On-Resistance $I_{SW1}$ = 100mA         0.16         Ω           SW1 Leakage Current $V_{VP1}$ = 5.5V, $V_{SW1}$ = 0 or 5.5V         0         1 $\mu$ A           REG2           Maximum Output Current         1.1         A           Current Limit         1.55         1.8         2.05         A           PMOS On-Resistance $I_{SW2}$ = -100mA         0.16         Ω           NMOS On-Resistance $I_{SW2}$ = 100mA         0.16         Ω           SW2 Leakage Current $V_{VP2}$ = 5.5V, $V_{SW2}$ = 0 or 5.5V         0         1 $\mu$ A           REG3           Maximum Output Current         1.3         A           Current Limit         1.8         2.1         2.5         A           PMOS On-Resistance $I_{SW3}$ = -100mA         0.16         Ω           NMOS On-Resistance $I_{SW3}$ = 100mA         0.16         Ω	Maximum Output Current		1.1			Α
NMOS On-Resistance $I_{SW1}$ = 100mA         0.16         Ω           SW1 Leakage Current $V_{VP1}$ = 5.5V, $V_{SW1}$ = 0 or 5.5V         0         1 $\mu$ A           REG2           Maximum Output Current         1.1         A           Current Limit         1.55         1.8         2.05         A           PMOS On-Resistance $I_{SW2}$ = -100mA         0.16         Ω           NMOS On-Resistance $I_{SW2}$ = 100mA         0.16         Ω           SW2 Leakage Current $V_{VP2}$ = 5.5V, $V_{SW2}$ = 0 or 5.5V         0         1 $\mu$ A           REG3           Maximum Output Current         1.3         A           Current Limit         1.8         2.1         2.5         A           PMOS On-Resistance $I_{SW3}$ = -100mA         0.16         Ω           NMOS On-Resistance $I_{SW3}$ = 100mA         0.16         Ω	Current Limit		1.55	1.8	2.05	Α
SW1 Leakage Current $V_{VP1} = 5.5V$ , $V_{SW1} = 0$ or $5.5V$ 0         1         μA           REG2         Maximum Output Current         1.1         A           Current Limit         1.55         1.8         2.05         A           PMOS On-Resistance $I_{SW2} = -100$ mA         0.16         Ω           NMOS On-Resistance $I_{SW2} = 100$ mA         0.16         Ω           SW2 Leakage Current $V_{VP2} = 5.5V$ , $V_{SW2} = 0$ or $5.5V$ 0         1         μA           REG3           Maximum Output Current         1.3         A           Current Limit         1.8         2.1         2.5         A           PMOS On-Resistance $I_{SW3} = -100$ mA         0.16         Ω           NMOS On-Resistance $I_{SW3} = 100$ mA         0.16         Ω	PMOS On-Resistance	I <sub>SW1</sub> = -100mA		0.16		Ω
REG2         Maximum Output Current       1.1       A         Current Limit       1.55       1.8       2.05       A         PMOS On-Resistance $I_{SW2} = -100 \text{mA}$ 0.16       Ω         NMOS On-Resistance $I_{SW2} = 100 \text{mA}$ 0.16       Ω         SW2 Leakage Current $V_{VP2} = 5.5 \text{V}$ , $V_{SW2} = 0 \text{ or } 5.5 \text{V}$ 0       1 $\mu \text{A}$ REG3         Maximum Output Current       1.3       A         Current Limit       1.8       2.1       2.5       A         PMOS On-Resistance $I_{SW3} = -100 \text{mA}$ 0.16       Ω         NMOS On-Resistance $I_{SW3} = 100 \text{mA}$ 0.16       Ω	NMOS On-Resistance	I <sub>SW1</sub> = 100mA		0.16		Ω
Maximum Output Current1.1ACurrent Limit1.551.82.05APMOS On-Resistance $I_{SW2} = -100 \text{mA}$ 0.16ΩNMOS On-Resistance $I_{SW2} = 100 \text{mA}$ 0.16ΩSW2 Leakage Current $V_{VP2} = 5.5 \text{V}$ , $V_{SW2} = 0 \text{ or } 5.5 \text{V}$ 01 $\mu \text{A}$ REG3Maximum Output Current1.3ACurrent Limit1.82.12.5APMOS On-Resistance $I_{SW3} = -100 \text{mA}$ 0.16ΩNMOS On-Resistance $I_{SW3} = 100 \text{mA}$ 0.16Ω	SW1 Leakage Current	$V_{VP1} = 5.5V$ , $V_{SW1} = 0$ or $5.5V$		0	1	μA
Current Limit       1.55       1.8       2.05       A         PMOS On-Resistance $I_{SW2} = -100 \text{mA}$ 0.16       Ω         NMOS On-Resistance $I_{SW2} = 100 \text{mA}$ 0.16       Ω         SW2 Leakage Current $V_{VP2} = 5.5 \text{V}$ , $V_{SW2} = 0 \text{ or } 5.5 \text{V}$ 0       1 $\mu \text{A}$ REG3         Maximum Output Current       1.3       A         Current Limit       1.8       2.1       2.5       A         PMOS On-Resistance $I_{SW3} = -100 \text{mA}$ 0.16       Ω         NMOS On-Resistance $I_{SW3} = 100 \text{mA}$ 0.16       Ω	REG2					
PMOS On-Resistance $I_{SW2}$ = -100mA0.16ΩNMOS On-Resistance $I_{SW2}$ = 100mA0.16ΩSW2 Leakage Current $V_{VP2}$ = 5.5V, $V_{SW2}$ = 0 or 5.5V01 $\mu$ AREG3Maximum Output Current1.3ACurrent Limit1.82.12.5APMOS On-Resistance $I_{SW3}$ = -100mA0.16ΩNMOS On-Resistance $I_{SW3}$ = 100mA0.16Ω	Maximum Output Current		1.1			Α
NMOS On-Resistance $I_{SW2}$ = 100mA0.16ΩSW2 Leakage Current $V_{VP2}$ = 5.5V, $V_{SW2}$ = 0 or 5.5V01 $\mu$ AREG3Maximum Output Current1.3ACurrent Limit1.82.12.5APMOS On-Resistance $I_{SW3}$ = -100mA0.16ΩNMOS On-Resistance $I_{SW3}$ = 100mA0.16Ω	Current Limit		1.55	1.8	2.05	Α
SW2 Leakage Current $V_{VP2} = 5.5V, V_{SW2} = 0 \text{ or } 5.5V$ 0 1 $\mu A$ REG3  Maximum Output Current 1.3 A  Current Limit 1.8 2.1 2.5 A  PMOS On-Resistance $I_{SW3} = -100 \text{mA}$ 0.16 $\Omega$ NMOS On-Resistance $I_{SW3} = 100 \text{mA}$ 0.16 $\Omega$	PMOS On-Resistance	I <sub>SW2</sub> = -100mA		0.16		Ω
REG3Maximum Output Current1.3ACurrent Limit1.82.12.5APMOS On-Resistance $I_{SW3} = -100 \text{mA}$ 0.16 $\Omega$ NMOS On-Resistance $I_{SW3} = 100 \text{mA}$ 0.16 $\Omega$	NMOS On-Resistance	I <sub>SW2</sub> = 100mA		0.16		Ω
Maximum Output Current       1.3       A         Current Limit       1.8       2.1       2.5       A         PMOS On-Resistance $I_{SW3} = -100$ mA       0.16       Ω         NMOS On-Resistance $I_{SW3} = 100$ mA       0.16       Ω	SW2 Leakage Current	$V_{VP2} = 5.5V$ , $V_{SW2} = 0$ or $5.5V$		0	1	μA
Current Limit1.82.12.5APMOS On-Resistance $I_{SW3}$ = -100mA0.16 $\Omega$ NMOS On-Resistance $I_{SW3}$ = 100mA0.16 $\Omega$	REG3					
PMOS On-Resistance $I_{SW3}$ = -100mA0.16ΩNMOS On-Resistance $I_{SW3}$ = 100mA0.16Ω	Maximum Output Current		1.3			Α
NMOS On-Resistance $I_{SW3} = 100 \text{mA}$ 0.16 $\Omega$	Current Limit		1.8	2.1	2.5	А
***	PMOS On-Resistance	I <sub>SW3</sub> = -100mA		0.16		Ω
SW3 Leakage Current $V_{VP3} = 5.5V$ , $V_{SW3} = 0$ or $5.5V$ 0 1 $\mu$ A	NMOS On-Resistance	I <sub>SW3</sub> = 100mA		0.16	_	Ω
	SW3 Leakage Current	V <sub>VP3</sub> = 5.5V, V <sub>SW3</sub> = 0 or 5.5V		0	1	μA

 $<sup>\</sup>odot$ :  $V_{NOM}$  refers to the nominal output voltage level for  $V_{OUT}$  as defined by the *Ordering Information* section.

②: IMAX Maximum Output Current.



#### LOW-NOISE LDO ELECTRICAL CHARACTERISTICS

(V<sub>INL</sub> = 3.6V, C<sub>OUT4</sub> = C<sub>OUT5</sub> = C<sub>OUT6</sub> = C<sub>OUT7</sub> = 3.3µF, LOWIQ[] = [0], T<sub>A</sub> = 25°C, unless otherwise specified.)

PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Operating Voltage Range		2.5		5.5	V
Output Voltage Assuracy	$V_{OUT} \ge 1.2V, T_A = 25^{\circ}C, I_{OUT} = 10mA$	-1%	$V_{NOM}^{\mathbb{O}}$	2%	V
Output Voltage Accuracy	$V_{OUT}$ < 1.2V, $T_A$ = 25°C, $I_{OUT}$ = 10mA	-2%	$V_{NOM}^{\mathbb{O}}$	4%	]
	$V_{INL}$ = Max ( $V_{OUT}$ + 0.5V, 3.6V) to 5.5V, LOWIQ[] = [0]		0.05		
Line Regulation	$V_{INL}$ = Max ( $V_{OUT}$ + 0.5V, 3.6V) to 5.5V LOWIQ[] = [1]		0.5		mV/V
Load Regulation	I <sub>OUT</sub> = 1mA to IMAX <sup>©</sup>		0.08		V/A
	f = 1kHz, I <sub>OUT</sub> = 20mA, V <sub>OUT</sub> =1.2V		75		
Power Supply Rejection Ratio	f = 10kHz, I <sub>OUT</sub> = 20mA, V <sub>OUT</sub> =1.2V		65		dB
	Regulator Enabled, LOWIQ[] = [0]		37	60	
Supply Current per Output	Regulator Enabled, LOWIQ[] = [1]		31	52	μA
	Regulator Disabled		0	1	1
Soft-Start Period	V <sub>OUT</sub> = 2.9V		140		μs
Power Good Threshold	V <sub>OUT</sub> Rising		89		%
Power Good Hysteresis	V <sub>OUT</sub> Falling		3		%
Output Noise	I <sub>OUT</sub> = 20mA, f = 10Hz to 100kHz, V <sub>OUT</sub> = 1.2V		50		$\mu V_{RMS}$
Discharge Resistance	LDO Disabled, DIS[] = 1		1.5		kΩ
REG4					
Dropout Voltage®	I <sub>OUT</sub> = 160mA, V <sub>OUT</sub> > 3.1V		90	180	mV
Maximum Output Current		320			mA
Current Limit®	V <sub>OUT</sub> = 95% of regulation voltage	370			mA
Stable C <sub>OUT4</sub> Range		3.3		20	μF
REG5	•				
Dropout Voltage	$I_{OUT} = 160 \text{mA}, V_{OUT} > 3.1 \text{V}$		140	280	mV
Maximum Output Current		320			mA
Current Limit	V <sub>OUT</sub> = 95% of regulation voltage	370			mA
Stable C <sub>OUT5</sub> Range		3.3		20	μF
REG6		<u> </u>			<u> </u>
Dropout Voltage	I <sub>OUT</sub> = 160mA, V <sub>OUT</sub> > 3.1V		90	180	mV
Maximum Output Current		320			mA
Current Limit	V <sub>OUT</sub> = 95% of regulation voltage	370			mA
Stable C <sub>OUT6</sub> Range		3.3		20	μF
REG7					
Dropout Voltage	I <sub>OUT</sub> = 160mA, V <sub>OUT</sub> > 3.1V		140	280	mV
Maximum Output Current		320			mA
Current Limit	V <sub>OUT</sub> = 95% of regulation voltage	370			mA
Stable C <sub>OUT7</sub> Range		3.3		20	μF

①: V<sub>NOM</sub> refers to the nominal output voltage level for V<sub>OUT</sub> as defined by the *Ordering Information* section.

②: IMAX Maximum Output Current.

③: Dropout Voltage is defined as the differential voltage between input and output when the output voltage drops 100mV below the regulation voltage (for 3.1V output voltage or higher).

<sup>4:</sup> LDO current limit is defined as the output current at which the output voltage drops to 95% of the respective regulation voltage. Under heavy overload conditions the output current limit folds back by 30% (typ)



## ActivePath<sup>™</sup> CHARGER ELECTRICAL CHARACTERISTICS

( $V_{CHGIN}$  = 5.0V,  $T_A$  = 25°C, unless otherwise specified.)

PARAMETER	TEST CONDITIONS		TYP	MAX	UNIT	
ActivePath	•	•			•	
CHGIN Operating Voltage Range		4.35		6.0	V	
CHGIN UVLO Threshold	CHGIN Voltage Rising	3.1	3.5	3.9	V	
CHGIN UVLO Hysteresis	CHGIN Voltage Falling		0.5		V	
CHGIN OVP Threshold	CHGIN Voltage Rising	6.0	6.6	7.2	V	
CHGIN OVP Hysteresis	CHGIN Voltage Falling		0.4		V	
	V <sub>CHGIN</sub> < V <sub>UVLO</sub>		35	70	μA	
CHGIN Supply Current	V <sub>CHGIN</sub> < V <sub>BAT</sub> + 50mV, V <sub>CHGIN</sub> > V <sub>UVLO</sub>		100	200	μA	
олол. оврр., овлол.	$V_{CHGIN} > V_{BAT} + 150 \text{mV}, V_{CHGIN} > V_{UVLO}$ Charger disabled, $I_{VSYS} = 0 \text{mA}$		1.3	2.0	mA	
CHGIN to VSYS On-Resistance	I <sub>VSYS</sub> = 100mA		0.3		Ω	
	ACIN = VSYS	1.5	2		Α	
CHGIN to VSYS Current Limit	ACIN = GA, CHGLEV = GA	80	90	100	A	
	ACIN = GA, CHGLEV = VSYS	400	450	500	mA	
VSYS REGULATION	•					
VSYS Regulated Voltage	I <sub>VSYS</sub> = 10mA	4.45	4.6	4.8	V	
nSTAT OUTPUT						
nSTAT Sink current	V <sub>nSTAT</sub> = 2V	4	8	12	mA	
nSTAT Leakage Current	$V_{\text{nSTAT}} = 4.2V$			1	μA	
ACIN AND CHGLEV INPUTS						
CHGLEV Logic High Input Voltage		1.4			V	
CHGLEV Logic Low Input Voltage				0.4	V	
CHGLEV Leakage Current	V <sub>CHGLEV</sub> = 4.2V			1	μA	
ACIN Voltage Thresholds	ACIN voltage rising	1.03	1.2	1.31	V	
ACIN Hysteresis voltage threshold	ACIN voltage falling		200		mV	
ACIN Leakage Current	V <sub>ACIN</sub> = 4.2V			1	μΑ	
TH INPUT	•	•			•	
TH Pull-Up Current	V <sub>CHGIN</sub> > V <sub>BAT</sub> + 100mV, Hysteresis = 50mV	91	102	110	μA	
V <sub>TH</sub> Upper Temperature Voltage Threshold (V <sub>THH</sub> )	Hot Detect NTC Thermistor	2.44	2.51	2.58	V	
V <sub>TH</sub> Lower Temperature Voltage Threshold (V <sub>THL</sub> )	Cold Detect NTC Thermistor	0.47	0.50	0.53	V	
V <sub>TH</sub> Hysteresis	Upper and Lower Thresholds		30		mV	



## ActivePath<sup>™</sup> CHARGER ELECTRICAL CHARACTERISTICS CONT'D

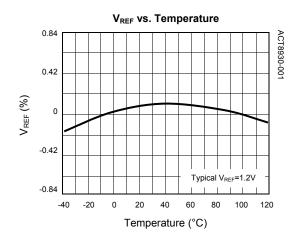
 $(V_{CHGIN} = 5.0V, T_A = 25^{\circ}C, unless otherwise specified.)$ 

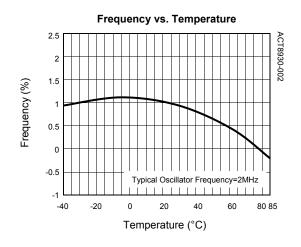
PARAMETER	TEST CONDITIONS		MIN	TYP	MAX	UNIT	
CHARGER							
BAT Reverse Leakage Current	V <sub>CHGIN</sub> = 0V, V	<sub>BAT</sub> = 4.2V, I <sub>VSYS</sub> = 0mA		8		μA	
BAT to VSYS On-Resistance				70		mΩ	
ISET Pin Voltage	Fast Charge			1.2		V	
ISET PIII VOItage	Precondition			0.13		V	
Charge Termination Voltage	$T_A = -20^{\circ}C$ to $T_A$	70°C	4.179	4.2	4.221	\ \	
Charge Termination Voltage	$T_A = -40^{\circ}C \text{ to } 8$	35°C	4.170	4.2	4.230	V	
		ACIN = VSYS, CHGLEV = VSYS	-10%	$I_{CHG}^{}{}^{\scriptscriptstyle{\oplus}}$	+10%		
Charge Current	$V_{BAT} = 3.8V$ ,	ACIN = VSYS, CHGLEV = GA	-10%	I <sub>CHG</sub> /5	+10%	A	
Charge Current	$R_{ISET} = 6.8k$	ACIN = GA, CHGLEV = VSYS	400	450	500	mA	
		ACIN = GA, CHGLEV = GA	80	90	100	1	
		ACIN = VSYS, CHGLEV = VSYS		10% I <sub>CHG</sub>			
Precondition Charge Current	$V_{BAT} = 2.7V$ , $R_{ISET} = 6.8k$	ACIN = VSYS, CHGLEV = GA		10% I <sub>CHG</sub>		mA	
Precondition Charge Current		ACIN = GA, CHGLEV = VSYS		45			
		ACIN = GA, CHGLEV = GA		45			
Precondition Threshold Voltage	V <sub>BAT</sub> Voltage F	Rising	2.75	2.85	3.0	V	
Precondition Threshold Hysteresis	V <sub>BAT</sub> Voltage F	alling		150		mV	
		ACIN = VSYS, CHGLEV = VSYS		10% I <sub>CHG</sub>			
END-OF-CHARGE Current	., , , , , , , , , , , , , , , , , , ,	ACIN = VSYS, CHGLEV = GA		10% I <sub>CHG</sub>		1	
Threshold	$V_{BAT} = 4.15V$	ACIN = GA, CHGLEV = VSYS		45		mA	
		ACIN = GA, CHGLEV = GA		45		!	
Charge Restart Threshold	V <sub>VSYS</sub> - V <sub>BAT</sub> , V <sub>BAT</sub> Falling		190	205	220	mV	
Precondition Safety Timer	PRETIMO[] = 10			80		min	
Total Safety Timer	TOTTIMO[] = 10			5		hr	
Thermal Regulation Threshold				100		°C	

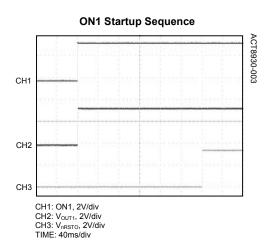
①:  $R_{ISET}(k\Omega) = 2336 \times (1V/I_{CHG}(mA)) - 0.205$ 

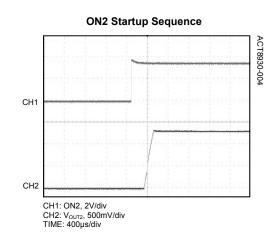


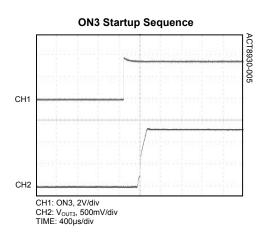
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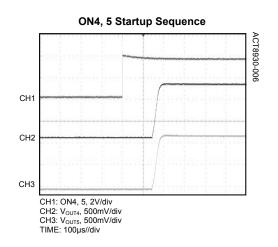






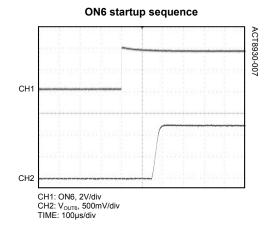


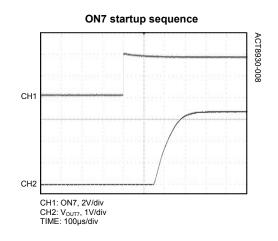


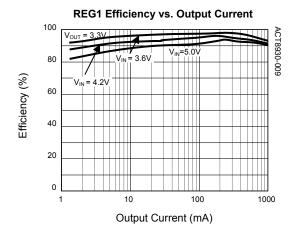


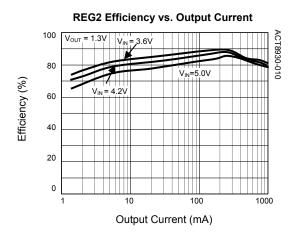


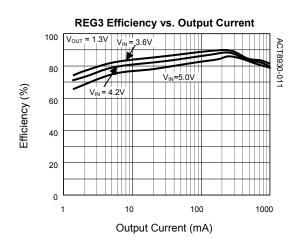
(T<sub>A</sub> = 25°C, unless otherwise specified.)





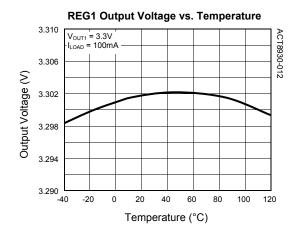


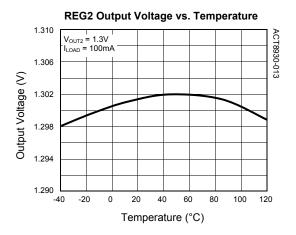


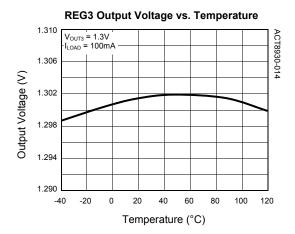


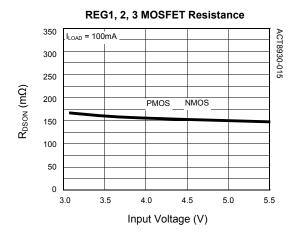
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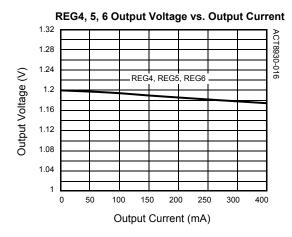


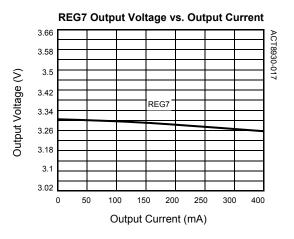


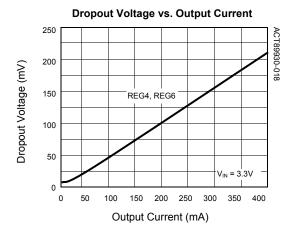


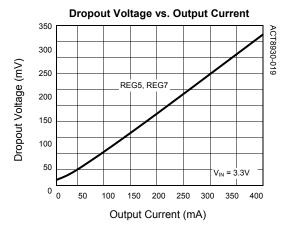




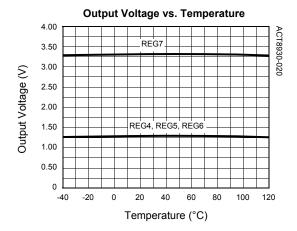


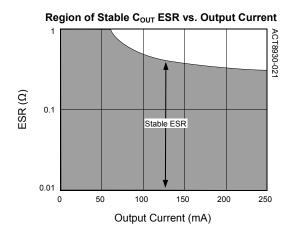


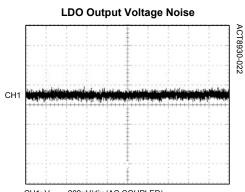






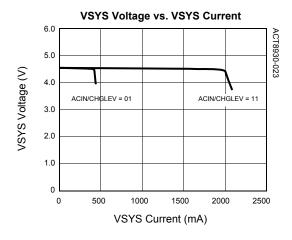


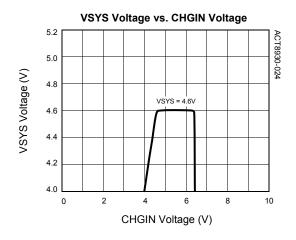


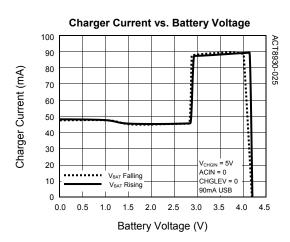


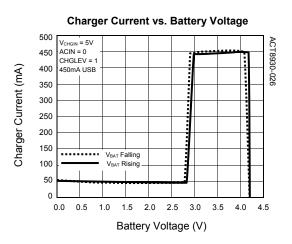
CH1:  $V_{OUTx}$ , 200 $\mu$ V/div (AC COUPLED) TIME: 200ms/div

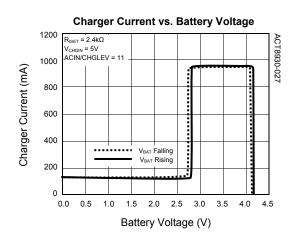


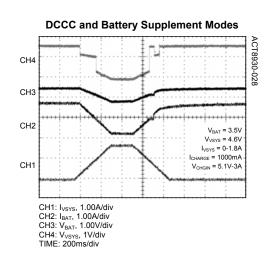




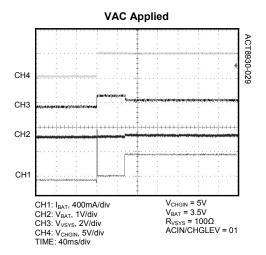


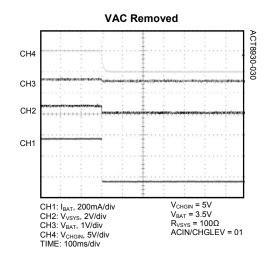


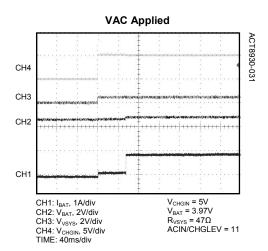


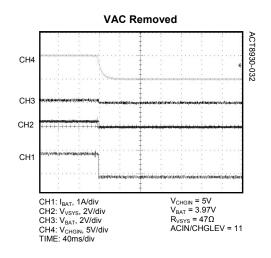














# SYSTEM CONTROL INFORMATION Control Signals

#### nRSTO Output

#### **Enable Inputs**

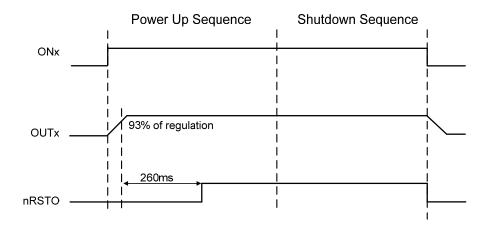
ON1, ON2, ON3, ON45, ON6 and ON7 are independent logic inputs for the regulators as shown in Table 2. Drive to logic high to enable the corresponding regulator(s); Drive to GA to disable.

nRSTO is an open-drain output which asserts low when any one or more of the regulator reaches the power-OK threshold. nRSTO remains low until the reset time-out period expires. Connect a  $10k\Omega$  or greater pull-up resistor from nRSTO to an appropriate voltage supply (typically OUT1).

Table 2: Control Pins

PIN NAME	REGULATOR(S)
ON1	OUT1
ON2	OUT2
ON3	OUT3
ON45	OUT4, OUT5
ON6	OUT6
ON7	OUT7

Figure 2: Enable/Disable Sequence





#### **FUNCTIONAL DESCRIPTION**

#### I<sup>2</sup>C Interface

The ACT8930 features an I<sup>2</sup>C interface that allows advanced programming capability to enhance overall system performance. To ensure compatibility with a wide range of system processors, the I<sup>2</sup>C interface supports clock speeds of up to 400kHz ("Fast-Mode" operation) and uses standard I<sup>2</sup>C commands. I<sup>2</sup>C write-byte commands are used to program the ACT8930, and I<sup>2</sup>C read-byte commands are used to read the ACT8930's internal registers. The ACT8930 always operates as a slave device, and is addressed using a 7-bit slave address followed by an eighth bit, which indicates whether the transaction is a read-operation or a write-operation, [1011011x].

SDA is a bi-directional data line and SCL is a clock input. The master device initiates a transaction by issuing a START condition, defined by SDA transitioning from high to low while SCL is high. Data is transferred in 8-bit packets, beginning with the MSB, and is clocked-in on the rising edge of SCL. Each packet of data is followed by an "Acknowledge" (ACK) bit, used to confirm that the data was transmitted successfully.

For more information regarding the I<sup>2</sup>C 2-wire serial interface, go to the NXP website: http://www.nxp.com.

#### **Housekeeping Functions**

#### Programmable System Voltage Monitor

The ACT8930 features a programmable system-voltage monitor, which monitors the voltage at VSYS and compares it to a programmable threshold voltage. The programmable voltage threshold is programmed by SYSLEV[3:0], as shown in Table 3.

SYSLEV[ ] is set to 3.0V by default. There is a 200mV rising hysteresis on SYSLEV[ ] threshold such that  $V_{VSYS}$  needs to be 3.2V(typ) or higher in order to power up the IC.

The nSYSSTAT[] bit reflects the output of an internal voltage comparator that monitors  $V_{\text{VSYS}}$  relative to the SYSLEV[] voltage threshold, the value of nSYSTAT[] = 1 when  $V_{\text{VSYS}}$  is lower than the SYSLEV[] voltage threshold, and nSYSTAT[] = 0 when  $V_{\text{VSYS}}$  is higher than the SYSLEV[] voltage threshold. Note that the SYSLEV[] voltage threshold is defined for falling voltages, and that the comparator produces about 200mV of hysteresis at VSYS. As a result, once  $V_{\text{VSYS}}$  falls below the SYSLEV threshold, its voltage must increase by more than about 200mV to clear that condition.

After the IC is powered up, the ACT8930 responds in one of two ways when the voltage at VSYS falls below the SYSLEV[] voltage threshold:

- 1) If nSYSMODE[] = 1 (default case), no action is taken by ACT8930.
- 2) If nSYSMODE[] = 0, when V<sub>VSYS</sub> falls below the programmable threshold the ACT8930 shuts down, immediately disabling all regulators. This option is useful for implementing a programmable "under-voltage lockout" function that forces the system off when the battery voltage falls below the SYSLEV threshold voltage. Since this option does not support a controlled shutdown sequence, it is generally used as a "fail-safe" to shut the system down when the battery voltage is too low.

Table 3: SYSLEV Falling Threshold

SYSLEV[3:0]	SYSLEV Falling Threshold (Hysteresis = 200mV)
0000	2.3
0001	2.4
0010	2.5
0011	2.6
0100	2.7
0101	2.8
0110	2.9
0111	3.0
1000	3.1
1001	3.2
1010	3.3
1011	3.4
1100	3.5
1101	3.6
1110	3.7
1111	3.8

#### Precision Voltage Detector

The LBI input connects to one input of a precision voltage comparator, which can be used to monitor a system voltage such as the battery voltage. An external resistive-divider network can be used to set voltage monitoring thresholds, as shown in *Functional Block Diagram*. The output of the comparator is present at the nLBO open-drain output.

#### Thermal Shutdown

The ACT8930 integrates thermal shutdown protection circuitry to prevent damage resulting from excessive thermal stress, as may be encountered under fault conditions. This circuitry disables all regulators if the ACT8930 die temperature exceeds 160°C, and prevents the regulators from being enabled until the IC temperature drops by 20°C (typ).



#### STEP-DOWN DC/DC REGULATORS

#### **General Description**

The ACT8930 features three synchronous, fixed-frequency, current-mode PWM step down converters that achieve peak efficiencies of up to 97%. REG3 is capable of supplying up to 1300mA of output current, while REG1 and REG2 support up to 1100mA. These regulators operate with a fixed frequency of 2MHz, minimizing noise in sensitive applications and allowing the use of small external components.

#### 100% Duty Cycle Operation

Each regulator is capable of operating at up to 100% duty cycle. During 100% duty-cycle operation, the high-side power MOSFET is held on continuously, providing a direct connection from the input to the output (through the inductor), ensuring the lowest possible dropout voltage in battery powered applications.

#### **Synchronous Rectification**

REG1, REG2, and REG3 each feature integrated nchannel synchronous rectifiers, maximizing efficiency and minimizing the total solution size and cost by eliminating the need for external rectifiers.

#### Soft-Start

When enabled, each output voltages tracks an internal 400µs soft-start ramp, minimizing input current during startup and allowing each regulator to power up in a smooth, monotonic manner that is independent of output load conditions.

#### Compensation

Each buck regulator utilizes current-mode control and a proprietary internal compensation scheme to simultaneously simplify external component selection and optimize transient performance over its full operating range. No compensation design is required; simply follow a few simple guidelines described below when choosing external components.

#### Input Capacitor Selection

The input capacitor reduces peak currents and noise induced upon the voltage source. A 4.7µF ceramic capacitor is recommended for each regulator in most applications.

#### Output Capacitor Selection

For most applications,  $22\mu F$  ceramic output capacitors are recommended for REG1, REG2, and REG3.

Despite the advantages of ceramic capacitors, care must be taken during the design process to ensure stable operation over the full operating voltage and temperature range. Ceramic capacitors are available in a variety of dielectrics, each of which exhibits different characteristics that can greatly affect performance over their temperature and voltage ranges.

Two of the most common dielectrics are Y5V and X5R. Whereas Y5V dielectrics are inexpensive and can provide high capacitance in small packages, their capacitance varies greatly over their voltage and temperature ranges and are not recommended for DC/DC applications. X5R and X7R dielectrics are more suitable for output capacitor applications, as their characteristics are more stable over their operating ranges, and are highly recommended.

#### **Inductor Selection**

REG1, REG2, and REG3 utilize current-mode control and a proprietary internal compensation scheme to simultaneously simplify external component selection and optimize transient performance over their full operating range. These devices were optimized for operation with 2.2µH inductors, although inductors in the 1.5µH to 3.3µH range can be used. Choose an inductor with a low DC-resistance, and avoid inductor saturation by choosing inductors with DC ratings that exceed the maximum output current by at least 30%.

#### **Configuration Options**

#### **Output Voltage Programming**

Each regulator powers up and regulates to its default output voltage. Once the system is enabled, each regulator's output voltage may be independently programmed to a different value, typically in order to minimize the power consumption of the microprocessor during some operating modes. Program the output voltages via the I<sup>2</sup>C serial interface by writing to the regulator's VSET[] register as shown in Table 4.

#### Enable / Disable Control

During normal operation, each buck may be enabled or disabled via the  $I^2C$  interface by writing to that regulator's ON[ ] bit. To regulator accept rising or falling edge of ON[ ] bit as on/off signal. To enable the regulator, clear ON[ ] to 0 first then set to 1. To disable the regulator, set ON[ ] to 1 first then clear it to 0.

#### **Operating Mode**

By default, REG1, REG2, and REG3 each operate in fixed-frequency PWM mode at medium to heavy

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loads, while automatically transitioning to a proprietary power-saving mode at light loads in order to maximize standby battery life. In applications where low noise is critical, force fixed-frequency PWM operation across the entire load current range, at the expense of light-load efficiency, by setting the MODE[] bit to 1.

#### Output OK[]

Each DC/DC features a power-OK status bit that can be read by the system microprocessor via the I<sup>2</sup>C interface. If an output voltage is lower than the power-OK threshold, typically 7% below the programmed regulation voltage, that regulator's OK[] bit will be 0.

#### **PCB Layout Considerations**

High switching frequencies and large peak currents make PC board layout an important part of step-down DC/DC converter design. A good design minimizes excessive EMI on the feedback paths and voltage gradients in the ground plane, both of which can result in instability or regulation errors.

Step-down DC/DCs exhibit discontinuous input current, so the input capacitors should be placed as close as possible to the IC, and avoiding the use of

via if possible. The inductor, input filter capacitor, and output filter capacitor should be connected as close together as possible, with short, direct, and wide traces. The ground nodes for each regulator's power loop should be connected at a single point in a starground configuration, and this point should be connected to the backside ground plane with multiple via. The output node for each regulator should be connected to its corresponding OUTx pin through the shortest possible route, while keeping sufficient distance from switching nodes to prevent noise injection. Finally, the exposed pad should be directly connected to the backside ground plane using multiple via to achieve low electrical and thermal resistance.

Table 4: REGx/VSET[] Output Voltage Setting

REGx/VSET[2:0]	REGx/VSET[5:3]							
REGX/VSET[2.0]	000	001	010	011	100	101	110	111
000	0.600	0.800	1.000	1.200	1.600	2.000	2.400	3.200
001	0.625	0.825	1.025	1.250	1.650	2.050	2.500	3.300
010	0.650	0.850	1.050	1.300	1.700	2.100	2.600	3.400
011	0.675	0.875	1.075	1.350	1.750	2.150	2.700	3.500
100	0.700	0.900	1.100	1.400	1.800	2.200	2.800	3.600
101	0.725	0.925	1.125	1.450	1.850	2.250	2.900	3.700
110	0.750	0.950	1.150	1.500	1.900	2.300	3.000	3.800
111	0.775	0.975	1.175	1.550	1.950	2.350	3.100	3.900



#### LOW-NOISE, LOW-DROPOUT LINEAR REGULATORS

#### **General Description**

REG4, REG5, REG6, and REG7 are low-noise, low-dropout linear regulators (LDOs) that supply up to 320mA. Each LDO has been optimized to achieve low noise and high-PSRR, achieving more than 65dB PSRR at frequencies up to 10kHz.

#### **Output Current Limit**

Each LDO contains current-limit circuitry featuring a current-limit fold-back function. During normal and moderate overload conditions, the regulators can support more than their rated output currents. During extreme overload conditions, however, the current limit is reduced by approximately 30%, reducing power dissipation within the IC.

#### Compensation

The LDOs are internally compensated and require very little design effort, simply select input and output capacitors according to the guidelines below.

#### Input Capacitor Selection

Each LDO requires a small ceramic input capacitor to supply current to support fast transients at the input of the LDO. Bypassing each INL pin to GA with 1µF. High quality ceramic capacitors such as X7R and X5R dielectric types are strongly recommended.

#### **Output Capacitor Selection**

Each LDO requires a small 3.3µF ceramic output capacitor for stability. For best performance, each output capacitor should be connected directly between the output and GA pins, as close to the output as possible, and with a short, direct connection. High quality ceramic capacitors such as X7R and X5R dielectric types are strongly recommended.

#### Configuration Options

#### **Output Voltage Programming**

By default, each LDO powers up and regulates to its default output voltage. Once the system is enabled, each output voltage may be independently programmed to a different value by writing to the regulator's VSET[] register via the I<sup>2</sup>C serial interface as shown in Table 4.

#### Enable / Disable Control

During normal operation, each LDO may be enabled or disabled via the I<sup>2</sup>C interface by writing to that LDO's ON[] bit. To regulator accept rising or falling edge of ON[] bit as on/off signal. To enable

the regulator, clear ON[ ] to 0 first then set to 1. To disable the regulator, set ON[ ] to 1 first then clear it to 0.

#### **Output Discharge**

Each of the ACT8930's LDOs features an optional output discharge function, which discharges the output to ground through a  $1.5k\Omega$  resistance when the LDO is disabled. This feature may be enabled or disabled by setting DIS[]; set DIS[] to 1 to enable this function, clear DIS[] to 0 to disable it.

#### Low-Power Mode

Each of ACT8930's LDOs features a LOWIQ[] bit which, when set to 1, reduces the LDO's quiescent current by about 16%, saving power and extending battery lifetime.

#### Output OK[]

Each LDO features a power-OK status bit that can be read by the system microprocessor via the interface. If an output voltage is lower than the power-OK threshold, typically 11% below the programmed regulation voltage, the value of that regulator's OK[] bit will be 0.

#### **PCB Layout Considerations**

The ACT8930's LDOs provide good DC, AC, and noise performance over a wide range of operating conditions, and are relatively insensitive to layout considerations. When designing a PCB, however, careful layout is necessary to prevent other circuitry from degrading LDO performance.

A good design places input and output capacitors as close to the LDO inputs and output as possible, and utilizes a star-ground configuration for all regulators to prevent noise-coupling through ground. Output traces should be routed to avoid close proximity to noisy nodes, particularly the SW nodes of the DC/DCs.

REFBP is a noise-filtered reference, and internally has a direct connection to the linear regulator controller. Any noise injected onto REFBP will directly affect the outputs of the linear regulators, and therefore special care should be taken to ensure that no noise is injected to the outputs via REFBP. As with the LDO output capacitors, the REFBP bypass capacitor should be placed as close to the IC as possible, with short, direct connections to the star-ground. Avoid the use of via whenever possible. Noisy nodes, such as from the DC/DCs, should be routed as far away from REFBP as possible.



## ActivePath<sup>™</sup> CHARGER

#### **General Description**

The ACT8930 features an advanced battery charger that incorporates the patent-pending *ActivePath architecture for system power selection*. This combination of circuits provides a complete, advanced battery-management system that automatically selects the best available input supply, manages charge current to ensure system power availability, and provides a complete, high-accuracy (±0.5%), thermally regulated, full-featured single-cell linear Li+ charger that can withstand input voltages of up to 12V.

#### ActivePath Architecture

The *ActivePath* architecture performs three important functions:

- 1) System Configuration Optimization
- 2) Input Protection
- 3) Battery-Management

#### **System Configuration Optimization**

The ActivePath circuitry monitors the state of the input supply, the battery, and the system, and automatically reconfigures itself to optimize the power system. If a valid input supply is present, ActivePath powers the system from the input while charging the battery in parallel. This allows the battery to charge as quickly as possible, while supplying the system. If a valid input supply is not present, ActivePath powers the system from the battery. Finally, if the input is present and the system current requirement exceeds the capability of the input supply, ActivePath allows system power to be drawn from both the battery and the input supply.

#### **Input Protection**

#### Input Over-Voltage Protection

The ActivePath circuitry features input over-voltage protection circuitry. This circuitry disables charging when the input voltage exceeds the voltage set by OVPSET[] as shown in Table 5, but stands off the input voltage in order to protect the system. Note that the adjustable OVP threshold is intended to provide the charge cycle with adjustable immunity against upward voltage transients on the input, and is not intended to allow continuous charging with input voltages above the charger's normal operating voltage range. Independent of the OVPSET[] setting, the charge cycle is not allowed to resume until the input voltage falls back into the charger's normal operating voltage range (i.e. below 6.0V).

In an input over-voltage condition this circuit limits  $V_{VSYS}$  to 4.6V, protecting any circuitry connected to VSYS from the over-voltage condition, which may exceed this circuitry's voltage capability. This circuit is capable of withstanding input voltages of up to 12V.

Table 5: Input Over-Voltage Protection Setting

OVPSET[1]	OVPSET[0]	OVP THRESHOLD
0	0	6.6V
0	1	7.0V
1	0	7.5V
1	1	8.0V

#### Input Supply Overload Protection

The ActivePath circuitry monitors and limits the total current drawn from the input supply to a value set by the ACIN and CHGLEV inputs, as well as the resistor connected to ISET. Drive ACIN to a logic-low for "USB Mode", which limits the input current to either 100mA, when CHGLEV is driven to a logic-low, or 450mA, when CHGLEV is driven to a logic-high. Drive ACIN to a logic-high for "AC-Mode", which limits the input current to 2A, typically.

#### Input Under Voltage Lockout

If the input voltage applied to CHGIN falls below 3.5V (typ), an input under-voltage condition is detected and the charger is disabled. Once an input under-voltage condition is detected, a new charge cycle will initiate when the input exceeds the under-voltage threshold by at least 500mV.

#### **Battery Management**

The ACT8930 features a full-featured, intelligent charger for Lithium-based cells, and was designed specifically to provide a complete charging solution with minimum system design effort.

The core of the charger is a CC/CV (Constant-Current/Constant-Voltage), linear-mode charge controller. This controller incorporates current and voltage sense circuitry, an internal  $70m\Omega$  power MOSFET, thermal-regulation circuitry, a full-featured state machine that implements charge control and safety features, and circuitry that eliminates the reverse blocking diode required by conventional charger designs.

The charge termination voltage is highly accurate  $(\pm 0.5\%)$ , and features a selection of charge safety time-out periods that protect the system from operation with damaged cells. Other features



include pin-programmable fast-charge current and one current-limited nSTAT output that can directly drive LED indicator or provide a logic-level status signal to the host microprocessor.

#### Dynamic Charge Current Control (DCCC)

The ACT8930's *ActivePath* charger features dynamic charge current control (DCCC) circuitry, which acts to ensure that the system remains powered while operating within the maximum output capability of the power adapter. The DCCC circuitry continuously monitors V<sub>VSYS</sub>, and if the voltage at VSYS drops by more than 200mV, the DCCC circuitry automatically reduces charge current in order to prevent V<sub>VSYS</sub> from continuing to drop.

#### **Charge Current Programming**

The ACT8930's *ActivePath* charger features a flexible charge current-programming scheme that combines the convenience of internal charge current programming with the flexibility of resistor based charge current programming. Current limits and charge current programming are managed as a function of the ACIN and CHGLEV pins, in combination with RISET, the resistance connected to the ISET pin.

ACIN is a logic input that configures the current-limit of *ActivePath*'s linear regulator as well as that of the battery charger. ACIN features a precise 1.2V logic threshold, so that the input voltage detection threshold may be adjusted with a simple resistive voltage divider. This input also allows a simple, low-cost dual-input charger switch to be implemented with just a few, low-cost components.

When the voltage at ACIN is above the 1.2V threshold, the charger operates in "AC-Mode" with a charge current programmed by RISET, and the RISET is given by:

 $R_{ISET}(k\Omega) = 2336 \times (1V/I_{CHG}(mA)) - 0.205$ 

With a given R<sub>ISET</sub> then charge current will reduce 5 times when CHGLEV is driven low.

When ACIN is below the 1.2V threshold, the charger operates in "USB-Mode", with a maximum CHGIN input current and charge current defined by

the CHGLEV input; 450mA, if CHGLEV is driven to a logic-high, or 100mA, if CHGLEV is driven to a logic-low.

The ACT8930's charge current settings are summarized in Table 6.

Note that the actual charge current may be limited to a current lower than the programmed fast charge current due to the ACT8930's internal thermal regulation loop. See the *Thermal Regulation* section for more information.

INDAT[] indicates the status of the CHGIN input supply. A value of 1 indicates that a valid CHGIN input (CHGIN UVLO Threshold<br/>
VCHGIN UVLO Threshold<br/>
VCHGIN CHGIN OVP Threshold) is present, a value of 0 indicates a valid input is not present. For example, in a dual-input charger application, knowing the state of the ACIN input can identify which type of input supply has been connected. The state of the ACIN input can be read at any time by reading the ACINSTAT[] bit, where a value of 1 indicates that the voltage at ACIN is above the 1.2V threshold (indicating that a wall-cube has been attached), and a value of 0 indicates that the voltage is below this threshold (indicating that ACIN input is not valid and USB supply input is selected).

#### **Charge-Control State Machine**

#### **PRECONDITION State**

A new charging cycle begins with the PRECONDITION state, and operation continues in this state until  $V_{BAT}$  exceeds the Precondition Threshold Voltage. When operating in PRECONDITION state, the cell is charged at 10% of the programmed maximum fast-charge constant current,  $I_{CHG}$ .

Once V<sub>BAT</sub> reaches the Precondition Threshold Voltage, the state machine jumps to the FAST-CHARGE state. If V<sub>BAT</sub> does not reach the Precondition Threshold Voltage before the Precondition Time-out period expires, then the state machine jumps to the TIME-OUT-FAULT state in order to prevent charging a damaged cell. See the Charge Safety Timers section for more information.

Table 6: ACIN and CHGLEV Inputs

ACIN	CHGLEV	CHARGE CURRENT (mA)	PRECONDITION CHARGE CURRENT (mA)
0	0	90	45
0	1	450	45
1	0	I <sub>CHG</sub> /5	10% × I <sub>CHG</sub>
1	1	I <sub>CHG</sub>	10% × I <sub>CHG</sub>

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Figure 3: Typical Li+ charge profile and ACT8930 charge states

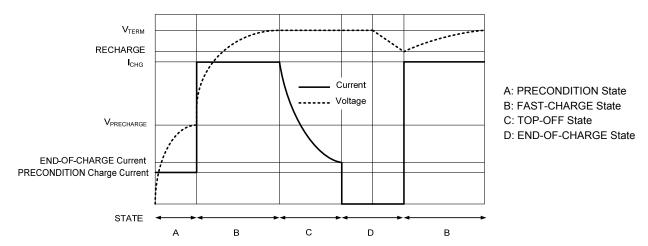
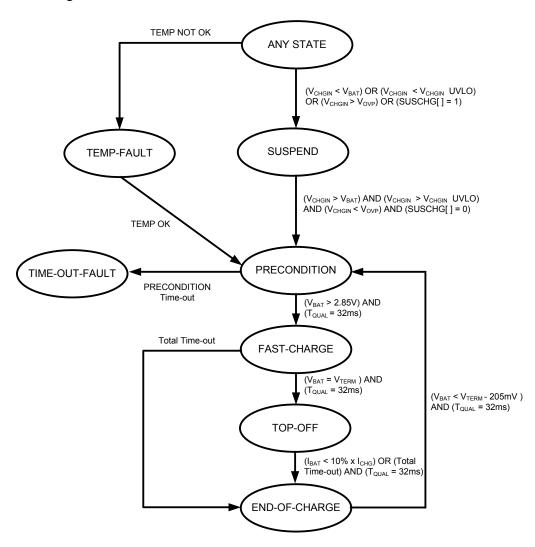


Figure 4: Charger State Diagram





#### **FAST-CHARGE State**

In the FAST-CHARGE state, the charger operates in constant-current (CC) mode and regulates the charge current to the current set by RISET. Charging continues in CC mode until VBAT reaches the charge termination voltage (VTERM), at which point the statemachine jumps to the TOP-OFF state. If VBAT does not reach VTERM before the total time out period expires then the state-machine will jump to the "EOC" state and will re-initiate a new charge cycle after 32ms "relax". See the Current Limits and Charge Current Programming sections for more information about setting the maximum charge current.

#### TOP-OFF State

In the TOP-OFF state, the cell charges in constant-voltage (CV) mode. In CV mode operation, the charger regulates its output voltage to the 4.20V charge termination voltage, and the charge current is naturally reduced as the cell approaches full charge. Charging continues until the charge current drops to END-OF-CHARGE current threshold, at which point the state machine jumps to the END-OF-CHARGE (EOC) state.

If the state-machine does not jump out of the TOP-OFF state before the Total-Charge Time-out period expires, the state machine jumps to the EOC state and will re-initiate a new charge cycle if  $V_{BAT}$  falls below termination voltage 205mV (typ). For more information about the charge safety timers, see the Charging Safety Times section.

#### END-OF-CHARGE (EOC) State

In the END-OF-CHARGE (EOC) state, the charger presents a high-impedance to the battery, minimizing battery current drain and allowing the cell to "relax". The charger continues to monitor the cell voltage, and re-initiates a charging sequence if the cell voltage drops to 205mV (typ) below the charge termination voltage.

#### SUSPEND State

The state-machine jumps to the SUSPEND state any time the battery is removed, and any time the input voltage either falls below the CHGIN UVLO threshold or exceeds the OVP threshold. Once none of these conditions are present, a new charge cycle initiates.

A charging cycle may also be suspended manually by setting the SUSPEND[] bit. In this case, initiate a new charging sequence by clearing SUSPEND[] to 0.

#### State Machine Status

The status of the charge state machine may be read at any time by reading CSTATE[0:1] to determine the current charging state.

Table 7: Charging Status Indication

CSTATE[0]	CSTATE[1]	STATE MACHINE STATUS
1	1	PRECONDITION State
1	0	FAST-CHARGE/ TOP-OFF State
0	1	END-OF-CHARGE State
0	0	SUSPEND/DISABLED/ FAULT State

#### **Thermal Regulation**

The charger features an internal thermal regulation loop that monitors die temperature and reduces charging current as needed to ensure that the die temperature does not exceed the thermal regulation threshold of 110°C. This feature protects against excessive junction temperature and makes the device more accommodating to aggressive thermal designs. Note, however, that attention to good thermal designs is required to achieve the fastest possible charge time by maximizing charge current.

#### **Charge Safety Timers**

The charger features programmable charge safety timers which help ensure a safe charge by detecting potentially damaged cells. These timers are programmable via the PRETIMO[1:0] and TOTTIMO[1:0] bits, as shown in Table 8 and Table 9. Note that in order to account for reduced charge current resulting from DCCC operation, the charge time-out periods are extended proportionally to the reduction in charge current. As a result, the actual safety period may exceed the nominal timer period.

The status of the charge timers may be read at any time by reading the TIMRDAT[] bit, where a value of 0 indicates that neither charge timer has expired, and a value of 1 indicates that one of the charge timers has expired.

PRETIMO[1]	PRETIMO[0]	PRECONDITION TIMEOUT PERIOD
0	0	40 mins
0	1	60 mins
1	0	80 mins
1	1	Disabled



Table 9: Total Safety Timer Setting

тоттімо[1]	тоттімо[0]	TOTAL TIME-OUT PERIOD
0	0	3 hrs
0	1	4 hrs
1	0	5 hrs
1	1	Disabled

#### **Charge Status Indicator**

The charger provides a charge-status indicator output, nSTAT. nSTAT is an open-drain output which sinks current when the charger is in an active-charging state, and is high-Z otherwise. nSTAT features an internal 8mA current limit, and is capable of directly driving a LED without the need of a current-limiting resistor or other external circuitry. To drive an LED, simply connect the LED between nSTAT pin and an appropriate supply, such as VSYS. For a logic-level charge status indication, simply connect a resistor from nSTAT to an appropriate voltage supply.

Table 10: Charging Status Indication

STATE	nSTAT	
PRECONDITION	Active	
FAST-CHARGE	Active	
TOP-OFF	Active	
END-OF-CHARGE	High-Z	
SUSPEND	High-Z	
TEMPERATURE FAULT	High-Z	
TIMEOUT FAULT	High-Z	

#### **Reverse-Current Protection**

The charger includes internal reverse-current protection circuitry that eliminates the need for blocking diodes, reducing solution size and cost as well as dropout voltage relative to conventional battery chargers. When the voltage at CHGIN falls below  $V_{\text{BAT}}$ , the charger automatically reconfigures its power switch to minimize current drawn from the battery.

#### **Battery Temperature Monitoring**

In a typical application, the TH pin is connected to the battery pack's thermistor input, as shown in Figure 5. The charger continuously monitors the temperature of the battery pack by injecting a  $102\mu A$  (typ) current into the thermistor (via the TH pin) and sensing the voltage at TH. The voltage at TH is continuously monitored, and charging is suspended if the voltage at TH exceeds either of the internal VTHH and VTHL thresholds of 0.5V and 2.51V, respectively.

The net resistance (from TH to GA) required to cross the thresholds are given by:

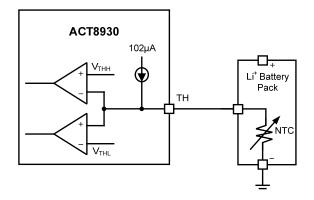
102 $\mu$ A × RNOM × kHOT = 0.5V  $\rightarrow$  RNOM × kHOT ≈ 5k $\Omega$ 

102 $\mu$ A × RNOM × kCOLD = 2.51V → RNOM × kCOLD ≈ 25k $\Omega$ 

where RNOM is the nominal thermistor resistance at room temperature, and kHOT and kCOLD represent the ratios of the thermistor's resistance at the desired hot and cold thresholds, respectively, to the resistance at 25°C.

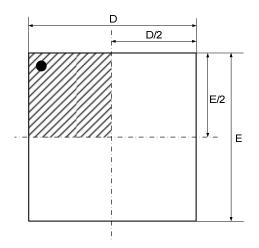
The status of the battery temperature pin may be read at any time by reading the TEMPDAT[] bit, where a value of 1 indicates that battery temperature is within the valid range, and a value of 0 indicates that battery temperature has exceeded either of the thresholds.

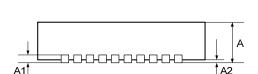
Figure 5: Simple Configuration

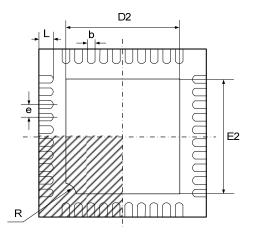




#### **TQFN55-40 PACKAGE OUTLINE AND DIMENSIONS**







SYMBOL	DIMENSION IN MILLIMETERS		DIMENSION IN INCHES	
	MIN	MAX	MIN	MAX
Α	0.700	0.800	0.028	0.031
A1	0.200 REF		0.008 REF	
A2	0.000	0.050	0.000	0.002
b	0.150	0.250	0.006	0.010
D	4.900	5.100	0.193	0.201
Е	4.900	5.100	0.193	0.201
D2	3.450	3.750	0.136	0.148
E2	3.450	3.750	0.136	0.148
е	0.400 BSC		0.016 BSC	
L	0.300	0.500	0.012	0.020
R	0.300		0.012	

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